

NJU2103A

System Reset IC

FEATURES

- Full compatible with NJM2103
 - Detection Voltage $V_{SA}=4.2V\pm1.0\%$
 - Adjustable Detection Voltage $V_{SB}=1.22V\pm1.0\%$
 - V_{SA} and V_{SB} have Hysteresis Characteristics at Reset release
 - Possible to detect Over Voltage $V_{SC}=1.235V\pm1.0\%$
 - Operating Temperature $T_a=-40$ to $125^{\circ}C$
 - Low Quiescent Current $280\mu A$ typ.
 - Reference Voltage can be taken out
 - Low reset operation voltage $0.8V$ typ.
 - Package DMP8, DIP8, TVSP8

GENERAL DESCRIPTION

The NJU2103A is a power supply voltage monitoring IC that instantaneously detects abnormality such as power supply voltage cutoff or drop and generates reset signal.

It can monitor 2 systems of 5 V power supply and arbitrarily set voltage.

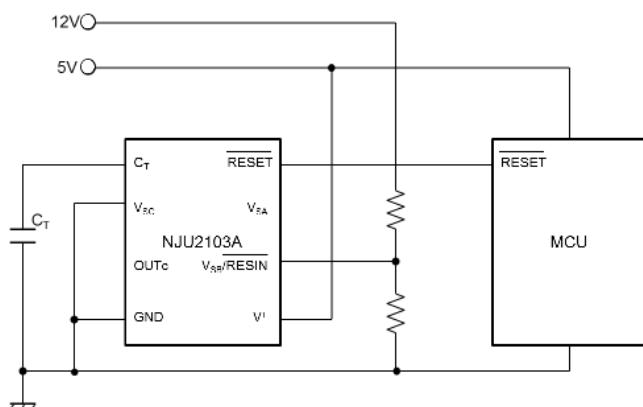
It is possible to direct replacement from NJM2103 and the small TVSP8 package is added.

Furthermore, it improves usability by extending operating temperature, standardizing AC characteristics, and making each parameter highly accurate.

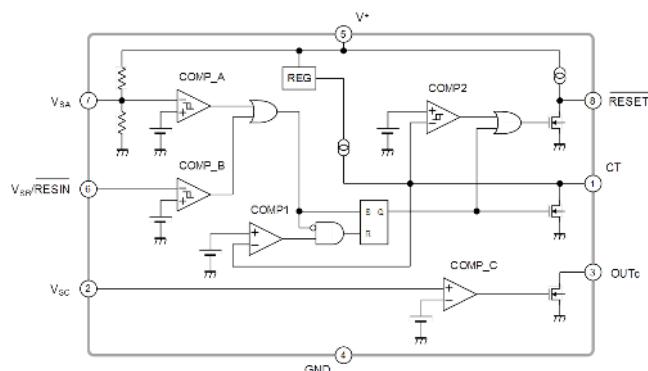
APPLICATIONS

- Industrial equipment
 - Housing and facility equipment
 - OA equipment
 - Amusement equipment

TYPICAL APPLICATION

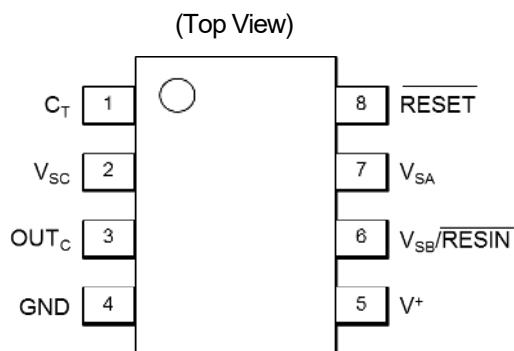


BLOCK DIAGRAM



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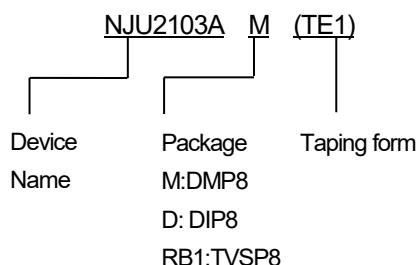
■PIN CONFIGURATION



DMP8/DIP8/TVSP8

PIN No.	PIN NAME	FUNCTION
1	C _T	Connects Capacitor pin for setting RESET Output Pulse Width
2	V _{SC}	Comparator C input pin
3	OUT _C	Comparator C output pin
4	GND	GND pin
5	V ⁺	Power Supply pin
6	V _{SB} /RESIN	Comparator B input pin
7	V _{SA}	Comparator A input pin
8	RESET	RESET output pin (Active Low)

■PRODUCT NAME INFORMATION



■ORDERING INFORMATION

PRODUCT NAME	PACKAGE OUTLINE	RoHS	Halogen-Free	TERMINAL FINISH	MARKING	WEIGHT (mg)	MOQ (pcs)
NJU2103AM(TE1)	DMP8	○	○	Sn-2Bi	2103A	95	2000
NJU2103AD	DIP8	○	-	Sn-2Bi	2103AD	510	2000
NJU2103ARB1(TE1)	TVSP8	○	○	Sn-2Bi	2103A	18	2000

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■ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Supply Voltage	V ⁺	-0.3 to 20	V
Input Voltage	V _{SA}	-0.3 to V ⁺ +0.3 (<20)	V
	V _{SB}	-0.3 to 20	V
	V _{SC}	-0.3 to 20	V
C _T Pin Voltage	V _{CT}	-0.3 to V ⁺ +0.3 (<20)	V
RESET Output Voltage	V _{RESET}	-0.3 to V ⁺ +0.3 (<20)	V
OUT _C Output Voltage	V _{OUTC}	-0.3 to 20	V
Power Dissipation(Ta=25°C)	P _D	(2-layer / 4-layer)	
DMP8		470 ⁽¹⁾ / 600 ⁽²⁾	mW
DIP8		910 ⁽¹⁾ / 1300 ⁽²⁾	
TVSP8		510 ⁽¹⁾ / 680 ⁽²⁾	
Junction Temperature	T _J	-40 to +150	°C
Operating Temperature	T _{opr}	-40 to +125	°C
Storage Temperature	T _{stg}	-50 to +150	°C

(1): Mounted on glass epoxy board.(76.2 x 114.3 x 1.6 :based on EIA/JEDEC standard, 2 Layers)

(2): Mounted on glass epoxy board.(76.2 x 114.3 x 1.6 :based on EIA/JEDEC standard, 4 Layers) internal Cu area: 74.2 x 74.2mm

■RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	RATINGS	UNIT
Supply Voltage	V ⁺	2.5 to 18	V
Input Voltage	V _{SA}	0 to V ⁺	V
	V _{SB}	0 to 18	V
	V _{SC}	0 to 18	V
Output Current	I _{RESET}	0 to 20	mA
	I _{OUTC}	0 to 6	mA
RESET Output Pulse Width	t _{PO}	0.15 to 1500	ms
C _T Capacitor	C _T	0.001 to 10	μF

ELECTRICAL CHARACTERISTICS**(DC Characteristics)**Unless other noted, $V^+=5V$, $V_{SB}=0V$, $V_{SC}=0V$, $C_T=0.01\mu F$, $T_a=25^\circ C$

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Operating Current 1	I_{CC1}	$V_{SB}=5V$	-	280	390	μA
Operating Current 2	I_{CC2}		-	300	410	μA
V _{SA} Detecting Voltage 1	V_{SAL}	V^+ sweep down, $V_{SB}=V^+$	4.158	4.200	4.242	V
		V^+ sweep down, $V_{SB}=V^+$, $T_a=-40^\circ C$ to $125^\circ C$	4.050	-	4.350	
V _{SA} Detecting Voltage 2	V_{SAH}	V^+ sweep up, $V_{SB}=V^+$	4.210	4.300	4.390	V
		V^+ sweep up, $V_{SB}=V^+$, $T_a=-40^\circ C$ to $125^\circ C$	4.150	-	4.450	
V _{SA} Hysteresis Width	V_{HRSA}		50	100	150	mV
V _{SB} Detecting Voltage	V_{SBL}	V_{SB} sweep down	1.208	1.220	1.232	V
		V_{SB} sweep down, $T_a=-40^\circ C$ to $125^\circ C$	1.190	-	1.250	
V _{SB} Detecting Supply Voltage Fluctuation	ΔV_{SBL}	$V^+=2.5$ to $18V$	-	3	10	mV
V _{SB} Hysteresis Width	V_{HRSB}		14	28	42	mV
V _{SB} Input Current 1	I_{IHB}	$V_{SB}=5V$	-	0	250	nA
V _{SB} Input Current 2	I_{ILB}		-	0	250	nA
High Level RESET Output Voltage	V_{OHR}	$I_{RESET}=-5\mu A$, $V_{SB}=5V$	4.5	4.9	-	V
RESET Output Saturation Voltage 1	V_{OLR1}	$I_{RESET}=3mA$	-	0.05	0.40	V
RESET Output Saturation Voltage 2	V_{OLR2}	$I_{RESET}=10mA$	-	0.15	0.50	V
RESET Output Sink Current	I_{RESET}	$V_{OLR}=1V$	20	60	-	mA
C_T Charge Current	I_{CT}	$V_{SB}=5V$, $V_{CT}=0.5V$	6	9	13	μA
V _{SC} Input Current1	I_{IHC}	$V_{SC}=5V$	-	0	500	nA
V _{SC} Input Current 2	I_{ILC}		-	0	500	nA
V _{SC} Detecting Voltage	V_{SC}		1.223	1.235	1.247	V
		$T_a=-40^\circ C$ to $125^\circ C$	1.195	-	1.275	
V _{SC} Detecting Supply Voltage Fluctuation	ΔV_{SC}	$V^+=2.5$ to $18V$	-	3	10	mV
OUT _C Output Leak Current	I_{OHC}	$V_{OHC}=18V$	-	0	1	μA
OUT _C Output Saturation Voltage	V_{OLC}	$I_{OUTC}=4mA$, $V_{SC}=5V$	-	0.15	0.40	V
OUT _C Output Sink Current	I_{OUTC}	$V_{OLC}=1V$, $V_{SC}=5V$	6	20	-	mA
RESET Minimum Operating Voltage	V^+_L	$V_{OLR}=0.4V$, $I_{RESET}=200\mu A$	-	0.8	1.2	V

ELECTRICAL CHARACTERISTICS**(AC Characteristics)**Unless other noted, $V^+=5V$, $V_{SB}=5V$, $V_{SC}=0V$, $C_T=0.01\mu F$, $T_a=25^\circ C$

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V_{SA} Input Pulse Width	t_{PIA}		5	-	-	μs
V_{SB} Input Pulse Width	t_{PIB}		5	-	-	μs
RESET Output Pulse Width	t_{PO}	$V_{SB}=V^+$	1.0	1.5	2.0	ms
RESET Rise Time	t_r	$V_{SB}=V^+$, $R_L=2.2k\Omega$, $C_L=100pF$ RESET=10% to 90%	-	1.0	1.5	μs
RESET Fall Time	t_f	$V_{SB}=V^+$, $R_L=2.2k\Omega$, $C_L=100pF$ RESET=90% to 10%	-	0.1	0.5	μs
Output Delay Time	t_{PD}	V_{SB} sweep down	-	2	10	μs
	t_{PHL}	V_{SC} sweep up, $R_L=2.2k\Omega$, $C_L=100pF$	-	0.5	-	μs
	t_{PLH}	V_{SC} sweep down, $R_L=2.2k\Omega$, $C_L=100pF$	-	1.0	-	μs

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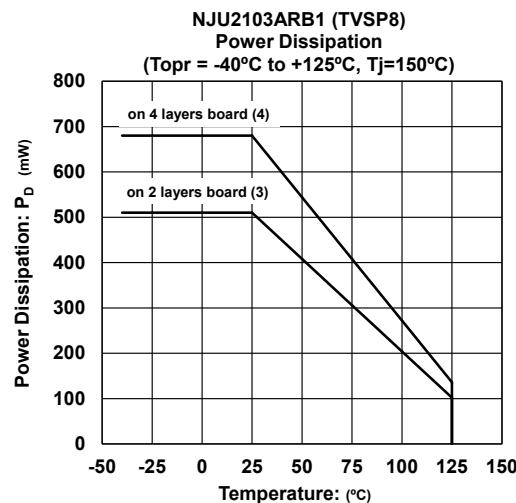
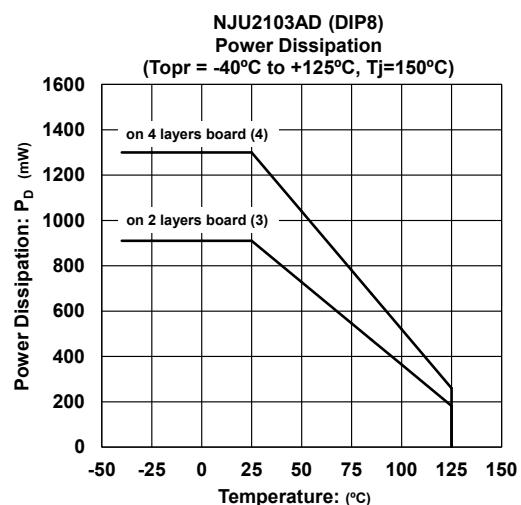
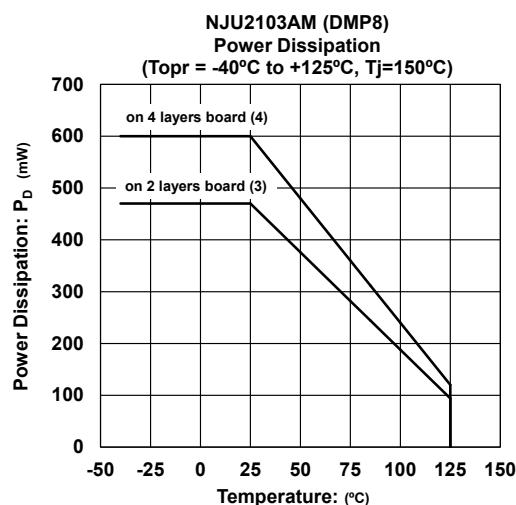
■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE		UNIT
Junction-to-ambient thermal resistance	θ_{ja}	DMP8	262 ⁽³⁾ 206 ⁽⁴⁾	°C/W
		DIP8	138 ⁽³⁾ 98 ⁽⁴⁾	
		TVSP8	244 ⁽³⁾ 185 ⁽⁴⁾	
Junction-to-Top of package characterization parameter	ψ_{jt}	DMP8	72 ⁽³⁾ 65 ⁽⁴⁾	°C/W
		DIP8	57 ⁽³⁾ 54 ⁽⁴⁾	
		TVSP8	51 ⁽³⁾ 45 ⁽⁴⁾	

(3): Mounted on glass epoxy board.(76.2 x 114.3 x 1.6 :based on EIA/JEDEC standard, 2 Layers)

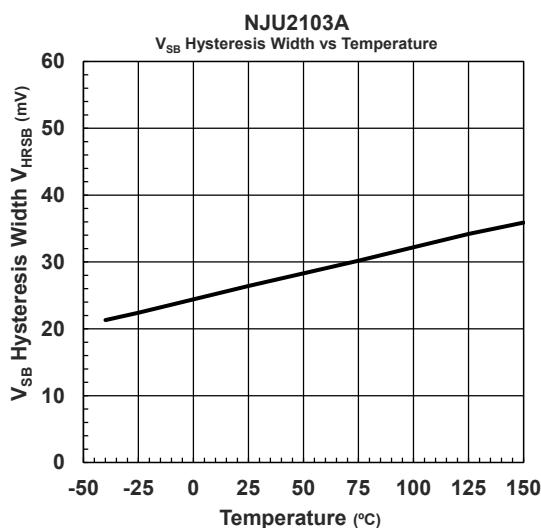
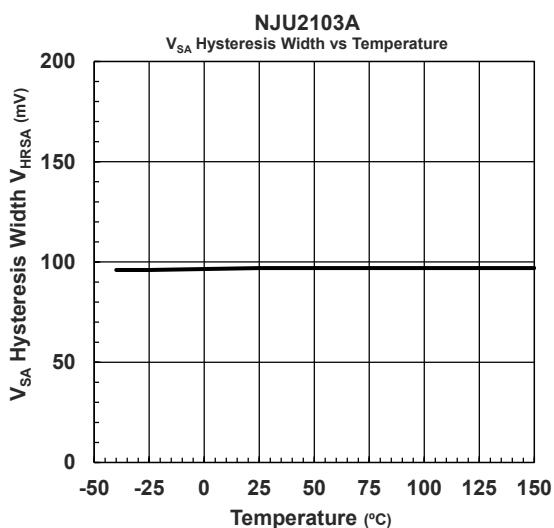
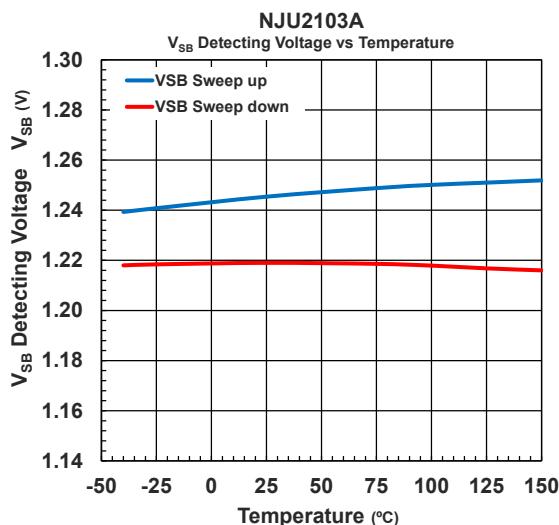
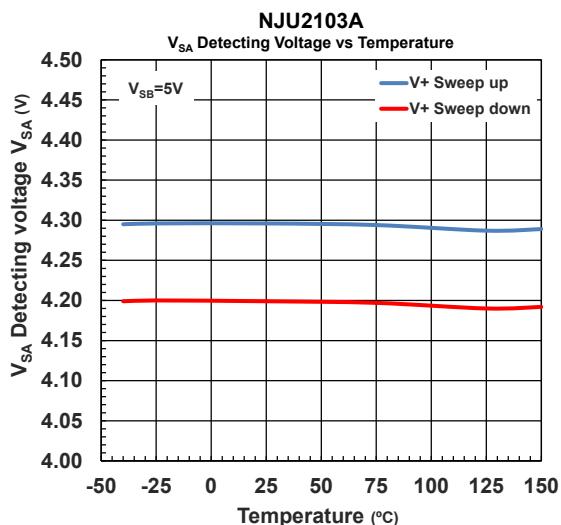
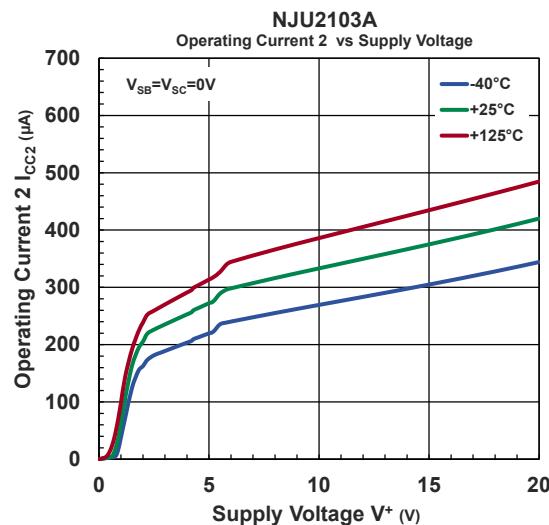
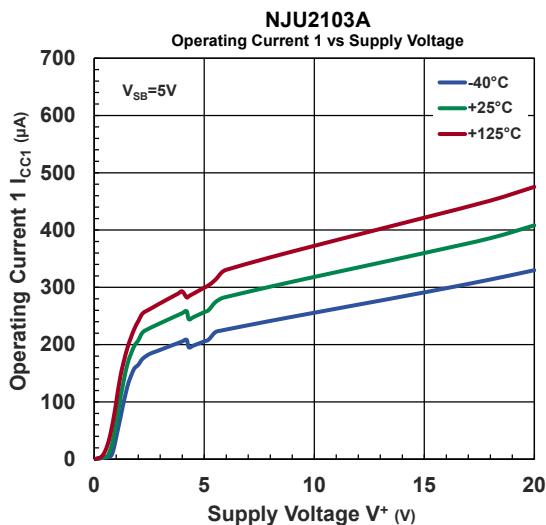
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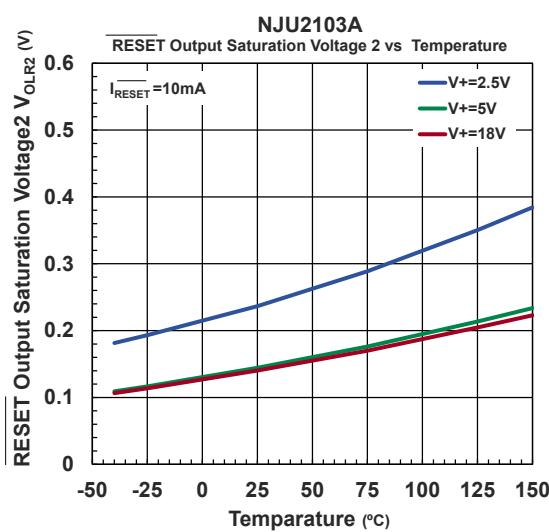
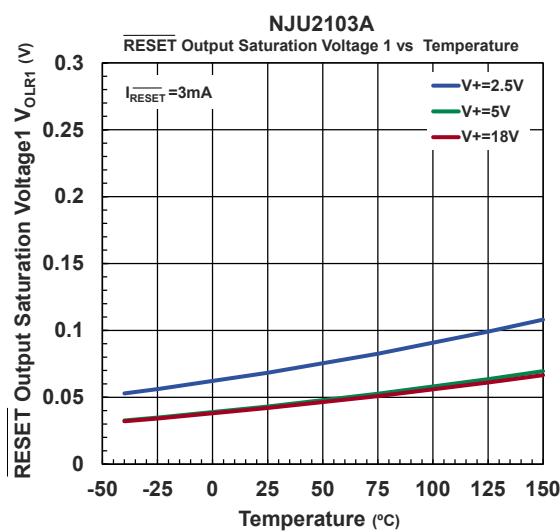
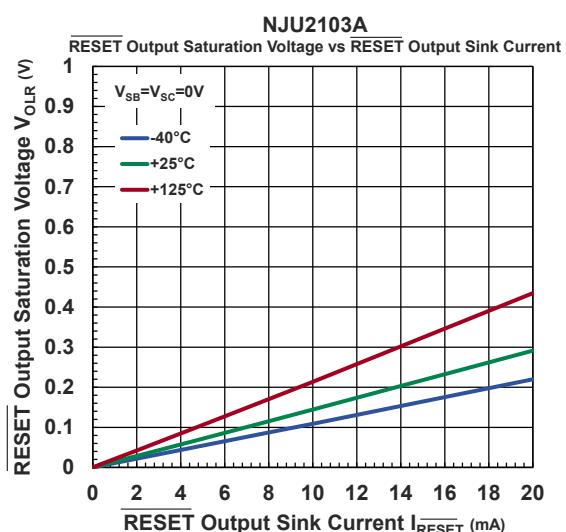
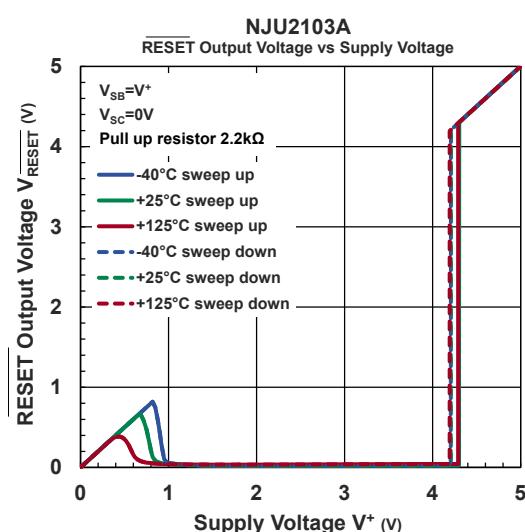
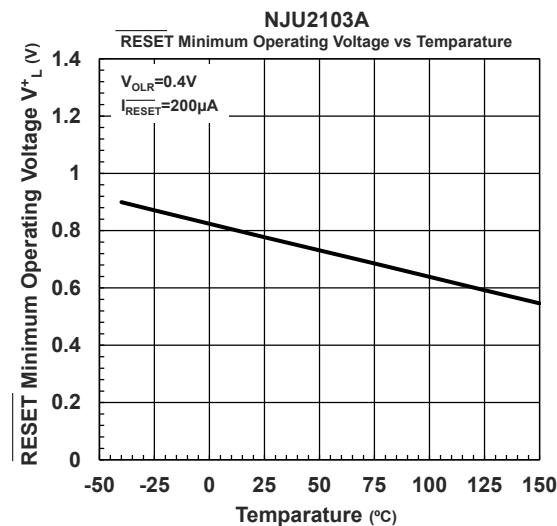
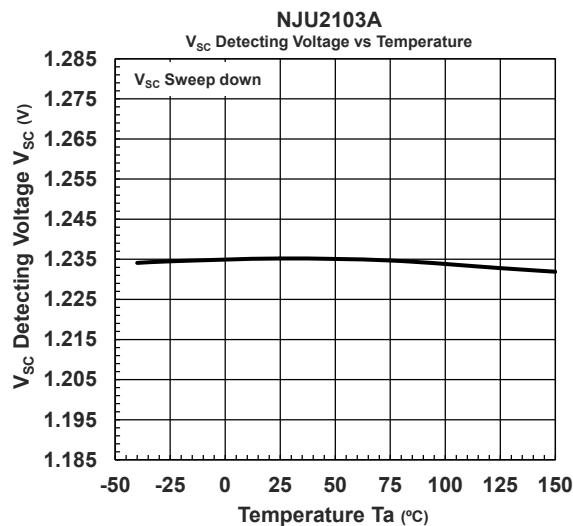
■ POWER DISSIPATION vs. AMBIENT TEMPERATURE

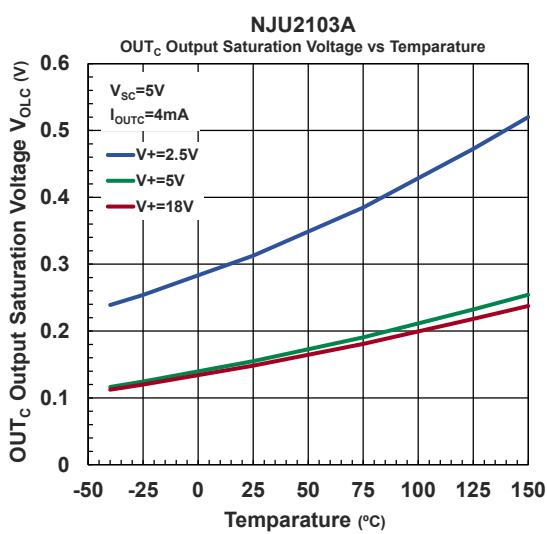
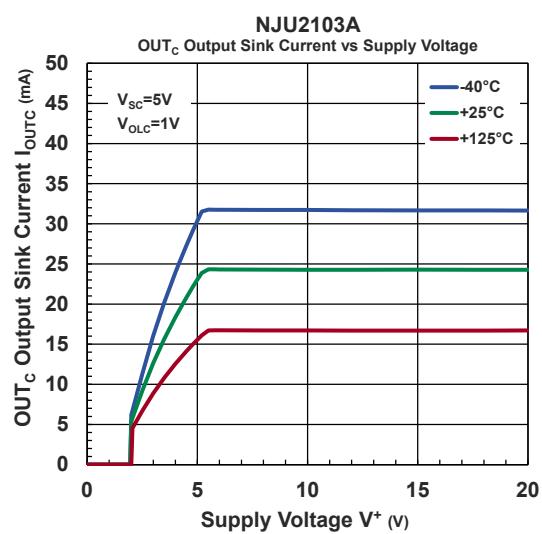
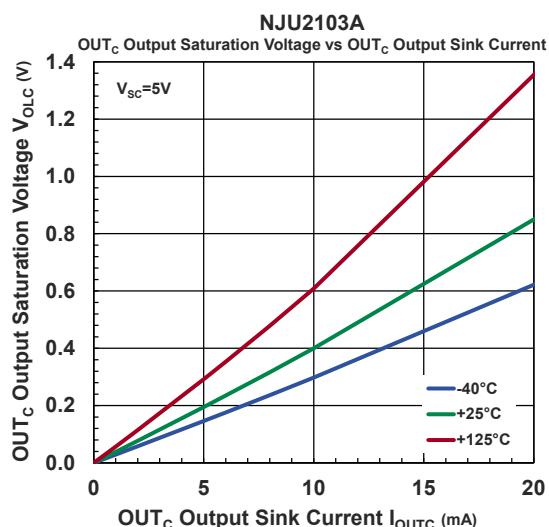
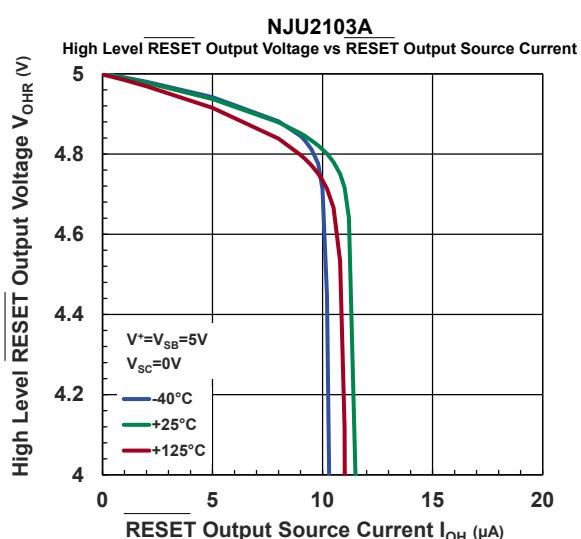
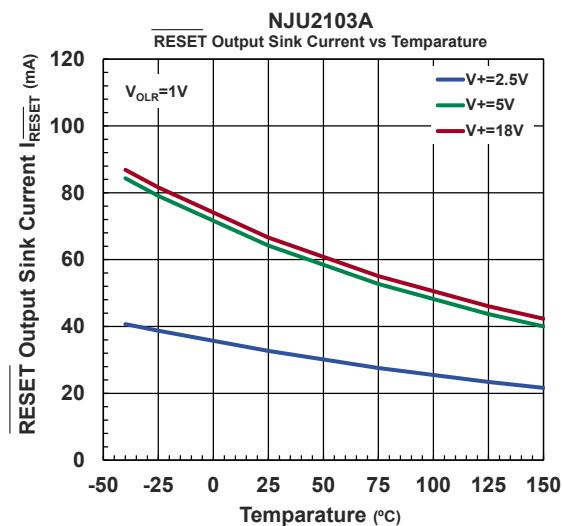
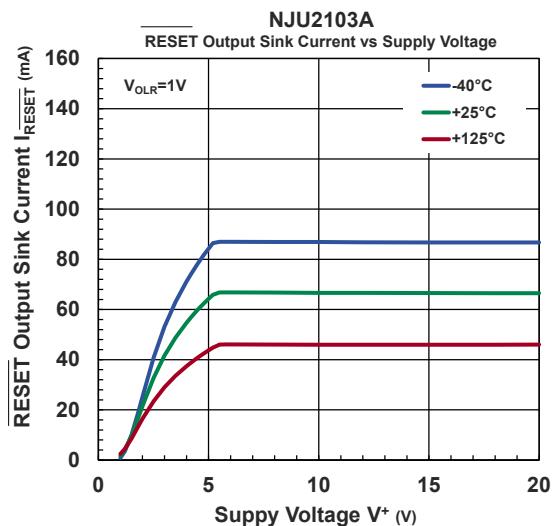


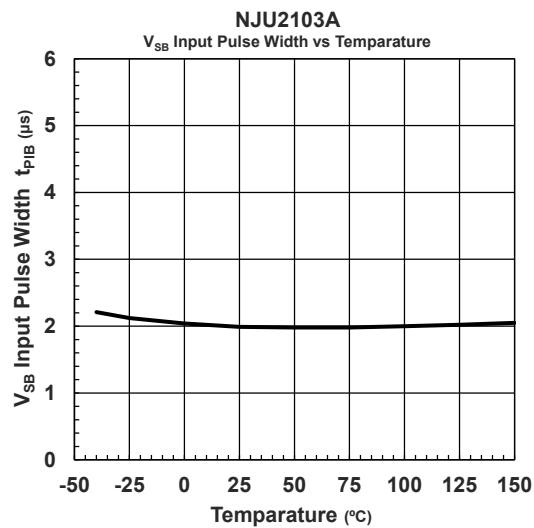
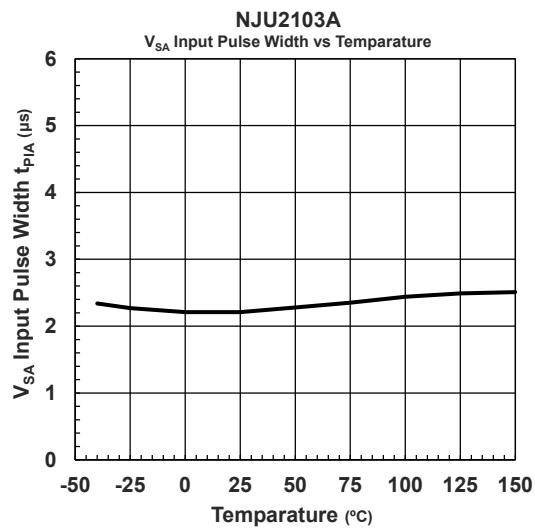
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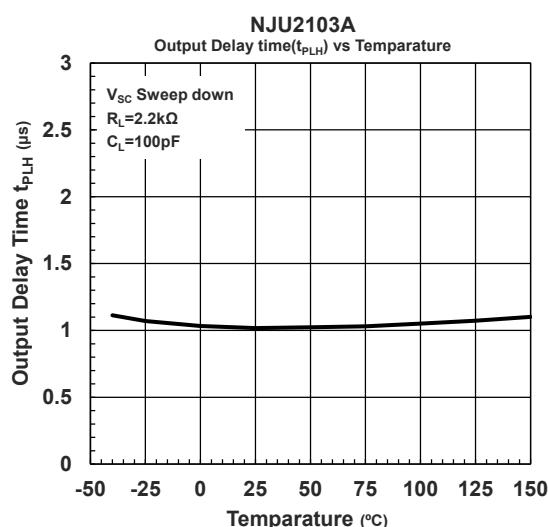
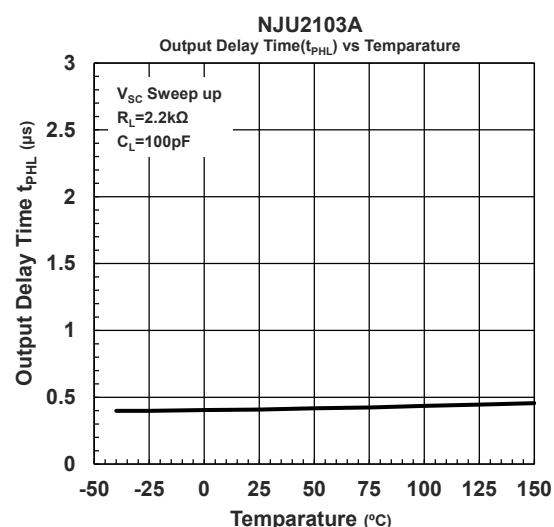
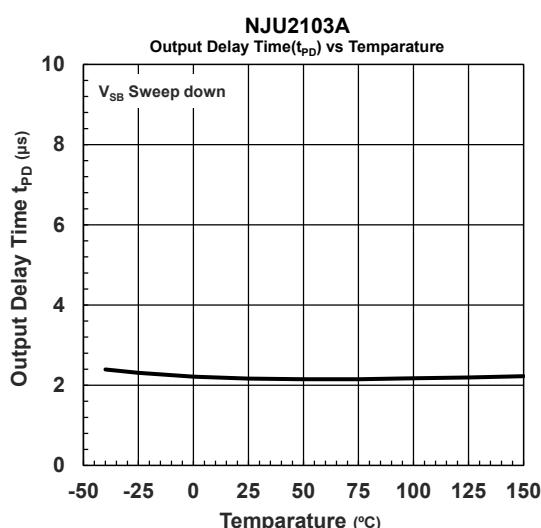
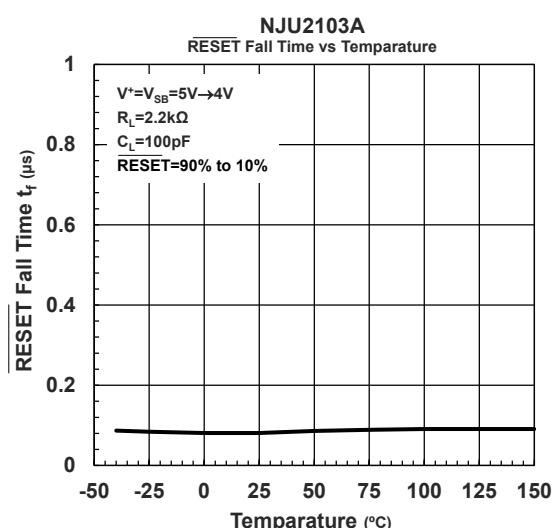
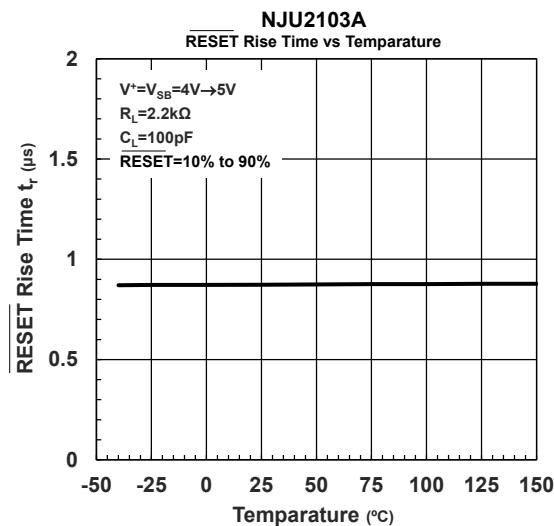
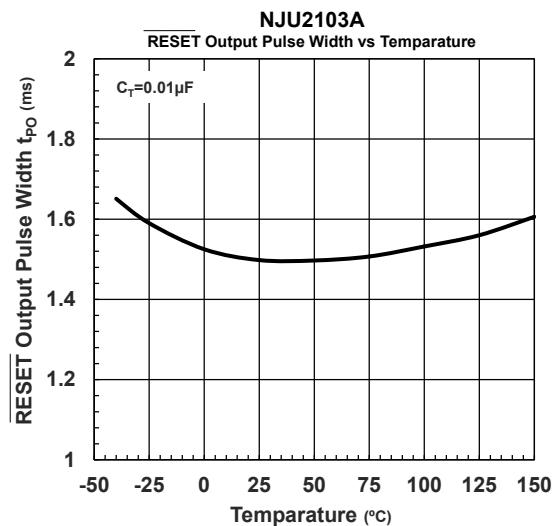
■TYPICAL CHARACTERISTICS

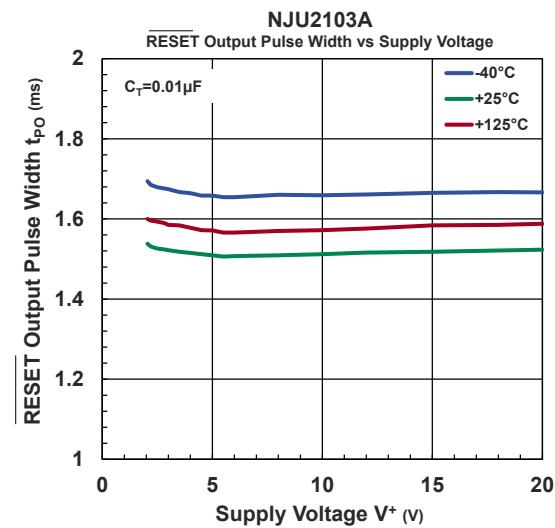
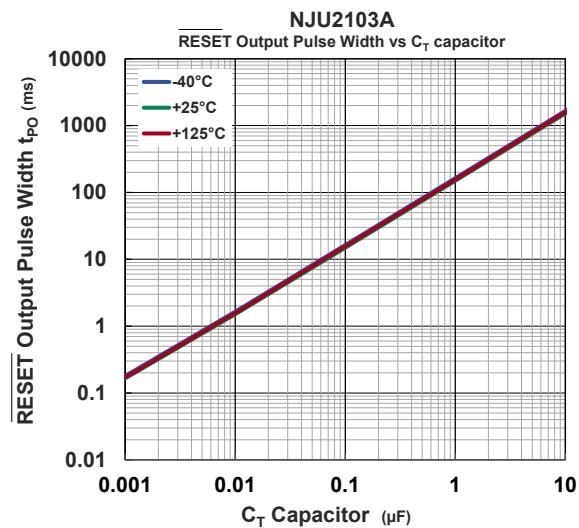










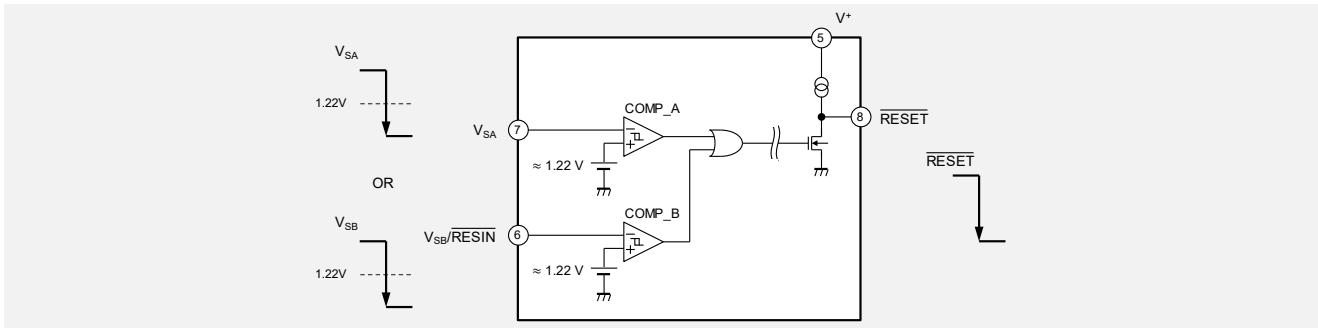


Technical Information

■FUNCTION EXPLANATION

COMP_A and COMP_B are comparator with hysteresis in detection voltage.

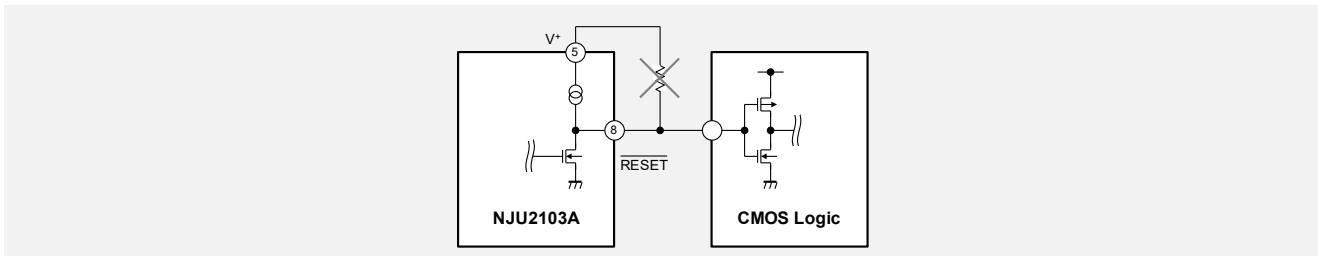
When either V_{SA} or V_{SB} pin voltage becomes about 1.22 V or less, the RESET output becomes "Low".



COMP_B can be used for arbitrary voltage detection (refer to Fig.3 or Fig.4) and also can be used as a manual reset function with reset hold time by TTL signal input. (refer to Fig.7)

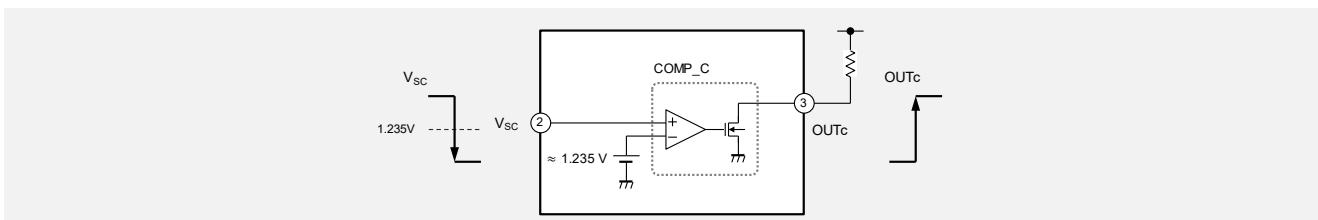
The NJU2103A can detect the instantaneous interruption and the instantaneous drop of the power line with a time of about 2 μ s width. If this level of instantaneous interruption or drop is not a problem, it can have a delayed trigger function by connecting capacitor to the V_{SA} and V_{SB} pins (refer to Fig.9).

Since the RESET pin is internally pulled up to V⁺, an external pull-up resistor isn't required in case of high impedance load like a CMOS logic IC.



COMP_C is an open-drain output comparator without hysteresis which has anti-polarity input and output.

Therefore, it can be used for overvoltage detection (refer to Fig.14), positive logic reset output (refer to Fig.8) and generating a reference voltage source.(refer to Fig.11 to 13)

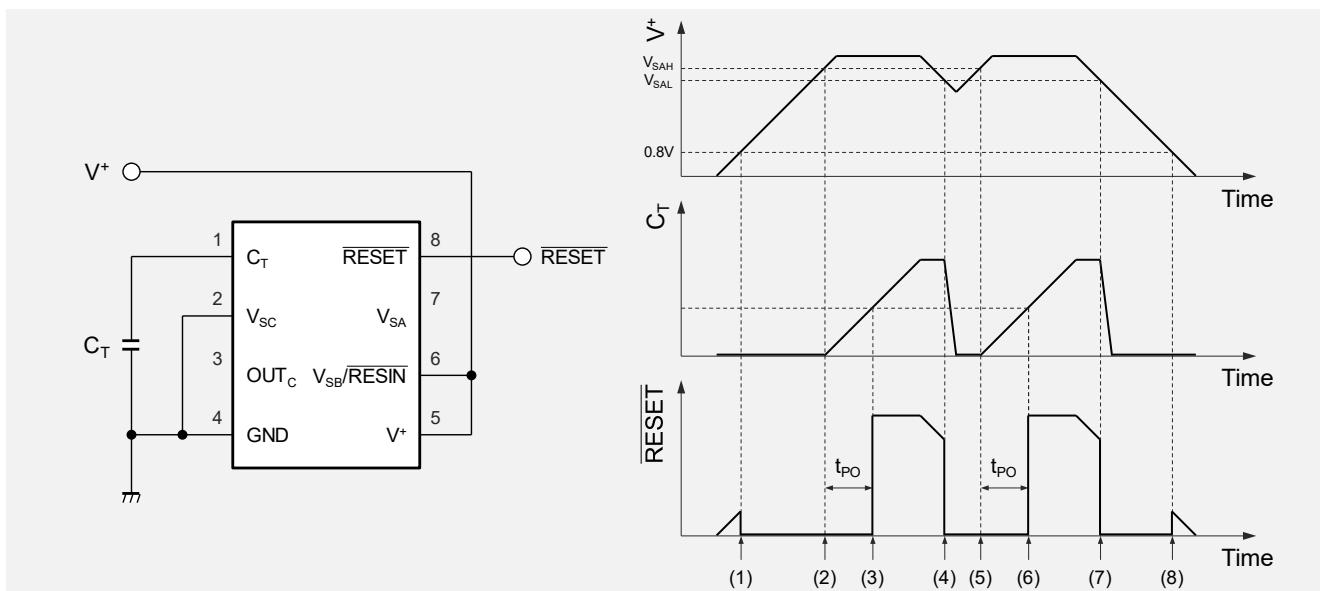


Unused Pin should be treated as shown in the table below.

Pin. No.	Pin Name	Treatment method of unused Pin
2	V _{sc}	Connect to GND
3	OUT _c	OPEN
6	V _{SB} /RESIN	Connect to V ⁺
7	V _{SA}	OPEN
8	RESET	OPEN

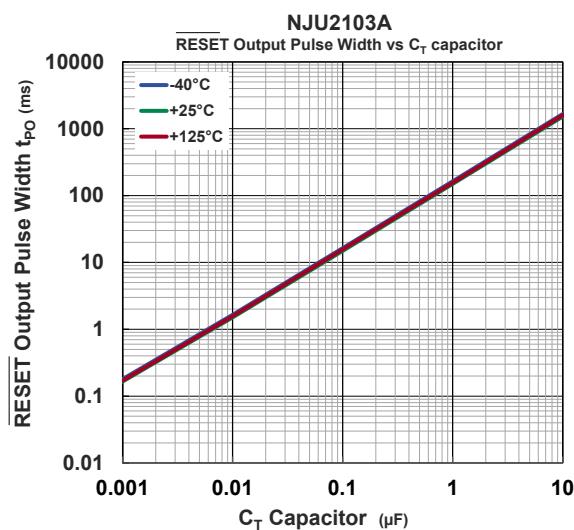
■ OPERATION EXPLANATION

Technical Information



- (1) When V^+ increases to about 0.8V, $\overline{\text{RESET}}$ becomes Low
- (2) When V^+ increases to V_{SAH} , charging to capacitor C_T starts. At this time, $\overline{\text{RESET}}$ holds Low.
- (3) $\overline{\text{RESET}}$ switches from Low to High after the $\overline{\text{RESET}}$ Output Pulse Width t_{PO} .
Refer to "Output Pulse Width vs C_T capacitor" in TYPICAL CHARACTERISTICS and t_{PO} can be calculated as following formula.

$$\overline{\text{RESET}} \text{ Output Pulse Width } t_{PO} [\text{ms}] \approx 150 \times C_T [\mu\text{F}]$$



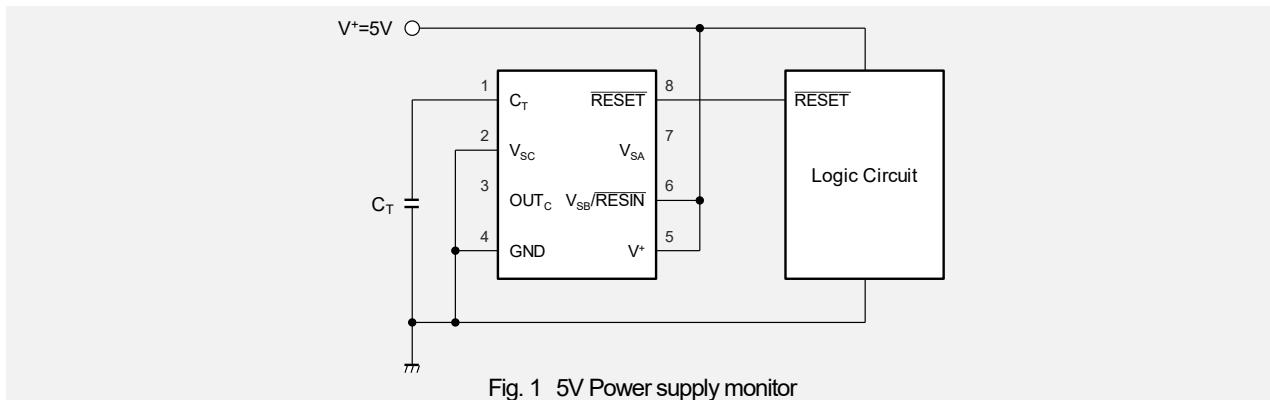
- (4) After $\overline{\text{RESET}}$ becomes High, When V^+ decreases below V_{SAL} , $\overline{\text{RESET}}$ goes Low and discharges C_T .
- (5) After V^+ decreases below V_{SAL} , it starts charging C_T when V^+ increase to V_{SAH} .
In case of instantaneous V^+ drop, if the time from V^+ decreases below V_{SAL} to increase to V_{SAH} is more than V_{SA} Input Pulse Width t_{PIA} , charging will start after discharging C_T .
- (6) V^+ increase to V_{SAH} and $\overline{\text{RESET}}$ switches from Low to High after $\overline{\text{RESET}}$ Output Pulse Width t_{PO}
- (7) When V^+ becomes less than V_{SAL} , repeat steps (4) – (6).
- (8) When V^+ decreases to 0 V, $\overline{\text{RESET}}$ holds Low until V^+ reaches about 0.8 V.

Technical Information

■ APPLICATION EXAMPLE

1. 5V Power supply monitor

Monitor the 5V power supply with V_{SA} (COMP_A). The detection voltage at falling is the V_{SA} detection voltage 1 V_{SAL} (4.2 V typ.), and the detection voltage at rising is the V_{SA} detection voltage 2 V_{SAH} (4.3Vtyp.).



2. Power supply monitor (adjust detection voltage by external resistor)

V_{SA} detection voltage1 can be adjusted with an external resistor.

- By selecting the external voltage-dividing resistors R_1 and R_2 to a sufficiently smaller value than internal voltage-dividing resistors R' , R'' (100 kΩ, 41 kΩ), the detection voltage can be set by the resistance ratio of R_1 and R_2 .

The formula for calculating detection voltage is as follows and refer to Tab.1 for setting example.

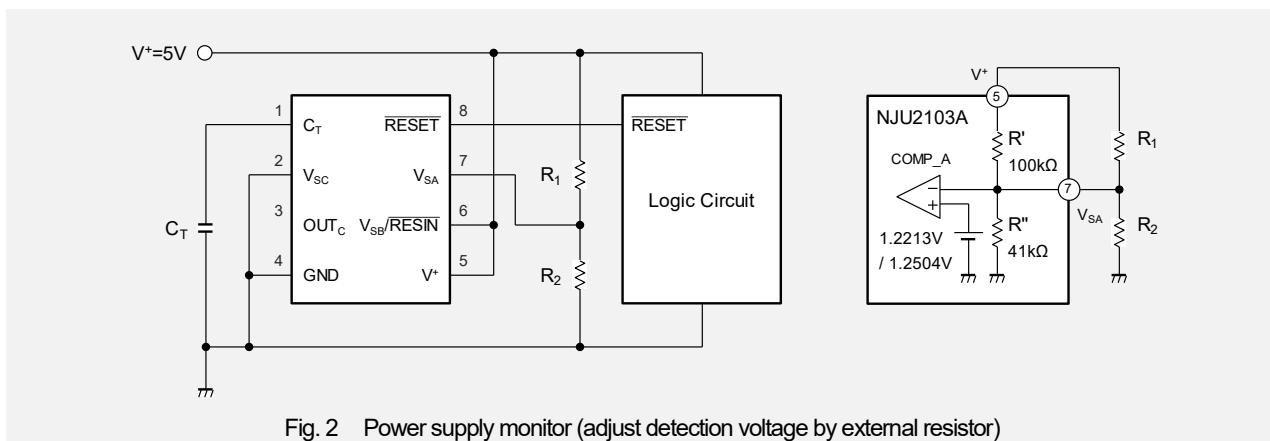
Detection voltage calculate formula ($R_1 \ll 100\text{k}\Omega$, $R_2 \ll 41\text{k}\Omega$)

$$\text{Detection Voltage(falling)} = \frac{(R_1 \parallel R') + (R_2 \parallel R'')} {R_2 \parallel R''} \times \frac{R''}{R' + R''} \times V_{SAL} \approx \frac{R_1 + R_2}{R_2} \times 1.2213 \text{ [V]}$$

$$\text{Detection Voltage(rising)} = \frac{(R_1 \parallel R') + (R_2 \parallel R'')} {R_2 \parallel R''} \times \frac{R''}{R' + R''} \times V_{SAH} \approx \frac{R_1 + R_2}{R_2} \times 1.2504 \text{ [V]}$$

Tab. 1 Setting example

External resistor R_1 [kΩ]	External resistor R_2 [kΩ]	Detection Voltage(falling) [V]	Detection Voltage(rising) [V]
6.2	2.4	4.37	4.47
12	5.1	4.11	4.20



Technical Information

3. Arbitrary power supply monitor (monitoring $V^+ \leq 18V$)

Monitor the power supply of $V^+ \leq 18V$ with V_{SB} (COMP_B) and voltage-dividing resistors R_1 and R_2 .

- The detection voltage can be set by resistors R_1 and R_2 .

The formula for calculating R_1 and R_2 is as follows and refer to Tab.2.

Detection voltage calculate formula

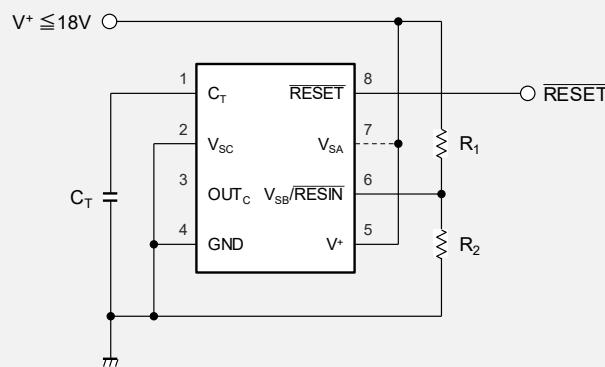
$$\text{Detection Voltage(falling)} = \frac{R_1 + R_2}{R_2} \times V_{SBL} \approx \frac{R_1 + R_2}{R_2} \times 1.220 \text{ [V]}$$

$$\text{Detection Voltage(rising)} = \frac{R_1 + R_2}{R_2} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_1 + R_2}{R_2} \times 1.248 \text{ [V]}$$

- When V^+ is 4.45V or less, connects V_{SA} (pin 7) to V^+ to disable COMP_A
- When V^+ is greater than 4.45 V, V_{SA} (pin 7) should be opened. And in this case, current consumption decreases. (decrease value: $17.3 \times V^+ [\mu\text{A}]$)

Tab. 2 setting example

External resistor R_1 [kΩ]	External resistor R_2 [kΩ]	Detection Voltage(falling) [V]	Detection Voltage(rising) [V]
43	16	4.50	4.60
22	15	3.01	3.08

Fig. 3 Arbitrary power supply monitor (monitoring $V^+ \leq 18V$)

Technical Information

4. Arbitrary power supply monitor (monitoring $V^+ > 18V$)

Monitor the power supply of $V^+ > 18V$ with V_{SB} (COMP_B) and voltage-dividing resistors R_1 and R_2 .

The power supply of this IC (about 5V) is generated with V_{SC} (COMP_C) and feedback resistors R_4 and R_5 .

- Set the detection voltage with resistors R_1 and R_2 according to the following formula.

Detection voltage calculate formula

$$Detection\ Voltage(V^+ \ falling) = \frac{R_1 + R_2}{R_2} \times V_{SBL} \approx \frac{R_1 + R_2}{R_1} \times 1.220 \text{ [V]}$$

$$Detection\ Voltage(V^{+}rising) = \frac{R_1 + R_2}{R_2} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_1 + R_2}{R_2} \times 1.248 \text{ [V]}$$

- The RESET output is $\approx 0V$ (low level) and $\approx 5V$ (high level). Not outputs V^+ voltage.
RESET should not be pulled up to V^+
 - If the resistor ratio of R_4 and R_5 is adjusted, high level RESET voltage is changed according to constant voltage set by resistor ratio of R_4 and R_5 . Constant voltage V_{OUT} is calculated as the following formula. However, shouldn't be exceed 18V.

$$\text{Constant Voltage } V_{OUT} = \frac{R_4 + R_5}{R_5} \times V_{SC} \approx \frac{R_4 + R_5}{R_5} \times 1.235 \text{ [V]}$$

- The constant voltage (5V output) can be used as the power supply for the small current consumption circuit.
 - When deciding the value of R_3 , it is necessary to be careful about power consumption.

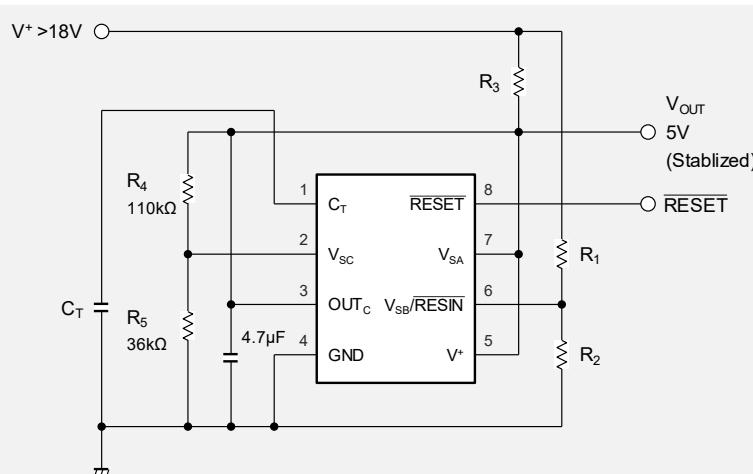


Fig. 4 Arbitrary power supply monitor (monitoring $V^+ > 18V$)

Technical Information

5. 5V, 12V power supply monitor (dual power supply monitor e.g. V⁺₁=5V, V⁺₂=12V)

Monitor the V⁺₁(5V) power supply with V_{SA}(COMP_A) and monitor the V⁺₂(12V) power supply with V_{SB} (COMP_B) and voltage-dividing resistors R₁ and R₂.

- V⁺₁ detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.
- V⁺₂ detection voltage (falling, rising) is set by R₁ and R₂ according to following formula. In case of resistor value in Fig.5, the detection voltage (falling) is about 9.0 V and the detection voltage (rising) is about 9.2 V.

V⁺₂detection voltage calculate formula

$$\text{Detection Voltage}(V_2^+\text{falling}) = \frac{R_1 + R_2}{R_2} \times V_{SBL} \approx \frac{R_1 + R_2}{R_2} \times 1.220 \text{ [V]}$$

$$\text{Detection Voltage}(V_2^+\text{rising}) = \frac{R_1 + R_2}{R_2} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_1 + R_2}{R_2} \times 1.248 \text{ [V]}$$

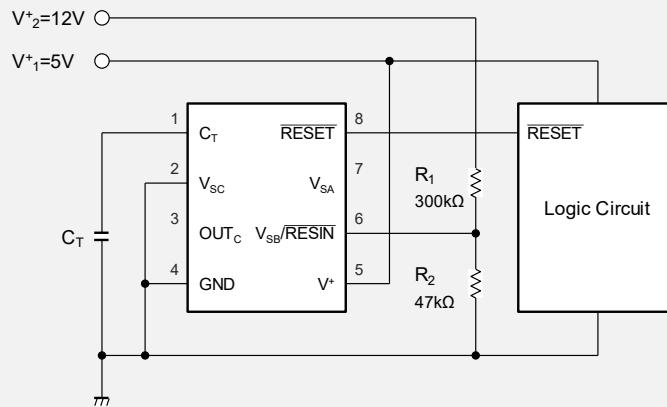


Fig. 5 5V, 12V power supply monitor (dual power supply monitor : V⁺₁=5V, V⁺₂=12V)

Technical Information

6. 5V, 12V power supply monitor (e.g. $V^+_1 = 5V$, $V^+_2 = 12V$, $\overline{\text{RESET}}$ output is only V^+_1 detection result)

Monitor the $V^+_1(5V)$ power supply with $V_{SA}(\text{COMP_A})$ and output signal from $\overline{\text{RESET}}$.

In addition, monitor the $V^+_2(12V)$ power supply with $V_{SC}(\text{COMP_C})$ and voltage-dividing resistors R_1, R_2, R_3, R_4 , NPN transistor., base current limiting resistor R_5 , and output signal from OUT_C .

- V^+_1 detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.
- V^+_2 detection voltage (falling) and hysteresis width at rising are calculated as following formula. In case of resistor value in Fig.6, the detection voltage (falling) is about 9.0 V and the hysteresis width at rising is about 0.2 V

 V^+_2 detection voltage and hysteresis width at rising calculate formula

$$\text{Detection Voltage}(V^+_2 \text{ falling}) = \frac{R_1 + R_2 + R_3}{R_2 + R_3} \times V_{SC} \approx \frac{R_1 + R_2 + R_3}{R_2 + R_3} \times 1.235 \text{ [V]}$$

$$\text{Hysteresis width at rising} = \frac{R_1(R_3 - R_3 \parallel R_4)}{(R_2 + R_3)(R_2 + R_3 \parallel R_4)} \times V_{SC} \approx \frac{R_1(R_3 - R_3 \parallel R_4)}{(R_2 + R_3)(R_2 + R_3 \parallel R_4)} \times 1.235 \text{ [V]}$$

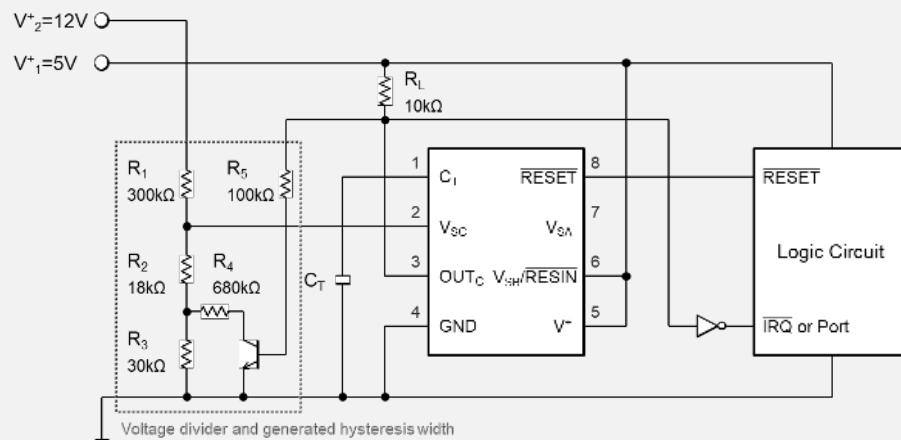


Fig. 6 5V, 12V power supply monitor ($V^+_1 = 5V$, $V^+_2 = 12V$, $\overline{\text{RESET}}$ output is only V^+_1 detection result)

7. Manual Reset function ($V^+ = 5V$)

By inputting the TTL signal to $V_{SB}/\overline{\text{RESIN}}$, it realizes manual reset output signal regardless of the state of V^+ .

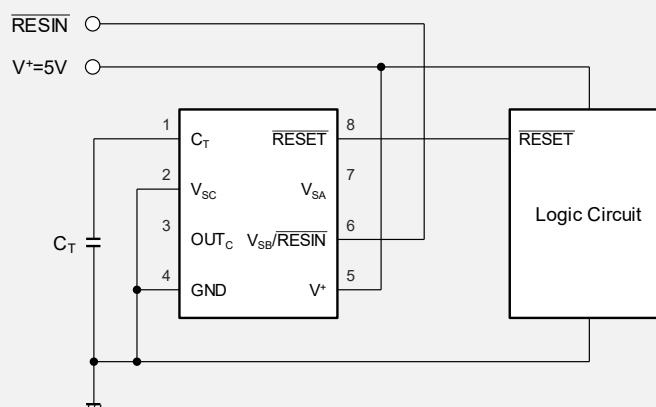


Fig. 7 Manual Reset function ($V^+ = 5V$)

Technical Information

8. Non-inverting reset output

If a positive output is required for reset signal, invert the $\overline{\text{RESET}}$ output with COMP_C and output from OUT_C. Since OUT_C is an open drain output, It is required the pull-up resistor.(shown as R_L in Fig.8)

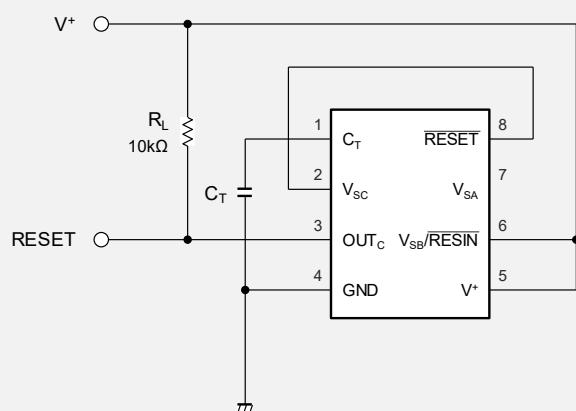


Fig. 8 Non-inverting reset output

9. Power supply voltage monitoring by delayed trigger

An arbitrary delay is added to the COMP_A operation by connecting capacitor C₁ between V_{SA} and GND.

When C₁ is connected minimum input pulse width becomes longer. E.g. t_{PI} = 40μs (C₁=1000pF)

Minimum input pulse width t_{PI} is calculated as following formula.

Minimum input pulse width calculate formula

$$t_{PI} [\mu\text{s}] \approx (R' \parallel R'') \times \ln\left(\frac{5 - 4}{V_{SAL} - 4}\right) \times 10^{-6} \times C_1 [\text{pF}] \approx 4.7 \times 10^{-2} \times C_1 [\text{pF}]$$

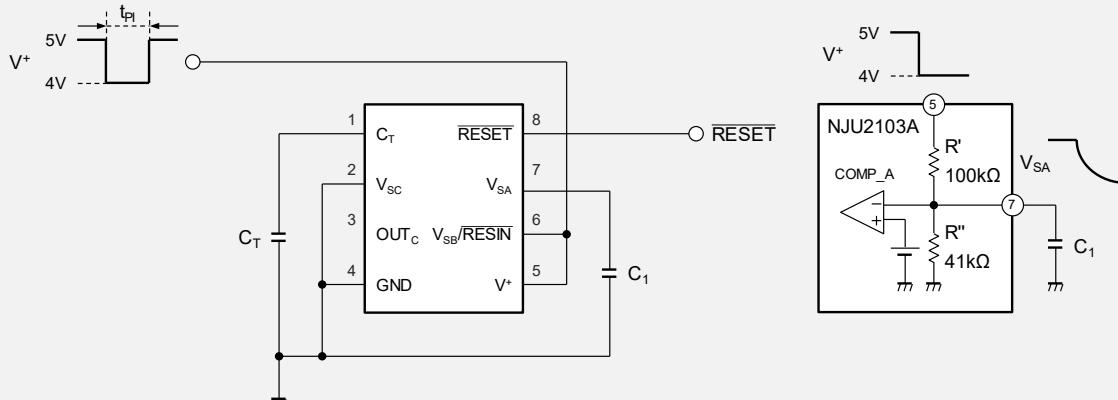


Fig. 9 Power supply voltage monitoring by delayed trigger

Technical Information

10. Positive and negative dual power supply monitoring (e.g. V⁺= 5V, V⁻=negative voltage)

Monitor the positive power supply with V_{SA} (COMP_A) and monitor the negative voltage with V_{SB} (COMP_B)

V_{SC} (COMP_C) is used to shift negative voltage to positive voltage.

- R₁, R₂, R₃ should have the same resistance value
- V⁺ detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.
- V⁻ detection voltage is calculated as following formula. In case of resistor value in Fig.10, the detection voltage (falling) is about -4.3V and the detection voltage (rising) is about -4.4V.

V⁻detection voltage calculate formula

$$\text{Detection voltage (V}^{\text{-falling}}\text{)} = \frac{R_3 + R_4}{R_3} \times V_{SC} - \frac{2R_4}{R_3} \times V_{SBL} \approx \frac{R_3 - R_4}{R_3} \times 1.220 \text{ [V]}$$

$$\text{Detection voltage(V}^{\text{-rising}}\text{)} = \frac{R_3 + R_4}{R_3} \times V_{SC} - \frac{2R_4}{R_3} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_3 - R_4}{R_3} \times 1.248 \text{ [V]}$$

- When using a power supply that outputs V⁻ without V⁺ output, it is necessary to connect a Schottky barrier diode (SBD) between the V_{SC} and GND to prevent being applied negative voltage to this IC.

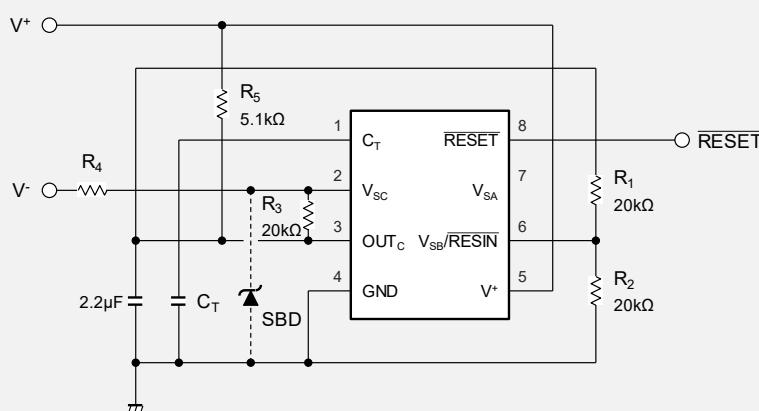


Fig. 10 Positive and negative dual power supply monitoring (V⁺= 5V, V⁻=negative voltage)

Technical Information

11. Reference voltage output and voltage drop monitoring (e.g. 9V reference output, 5V, 9V monitoring)

Monitor the V⁺(5V) power supply with V_{SA}(COMP_A).

9V Reference voltage V_{OUT} is generated by V_{SC}(COMP_C), feedback resistors R₃, R₄ and NPN transistor, and its 9V is monitored by V_{SB}(COMP_B) and voltage-dividing resistors R₁ and R₂.

- V⁺ detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.
- The reference voltage V_{OUT} and its detection voltage are calculated as the following formula. In case of resistor value in Fig.11, the reference voltage V_{OUT} is about 9.0V, the detection voltage (V_{OUT} falling) is about 7.1V and the detection voltage (V_{OUT} rising) is about 7.3V

Reference Voltage and detection voltage calculate formula

$$\text{Reference voltage } V_{OUT} = \frac{R_3 + R_4}{R_4} \times V_{SC} \approx \frac{R_3 + R_4}{R_4} \times 1.235 \text{ [V]}$$

$$\text{Detection Voltage}(V_{OUT} \text{ falling}) = \frac{R_1 + R_2}{R_2} \times V_{SBL} \approx \frac{R_1 + R_2}{R_2} \times 1.220 \text{ [V]}$$

$$\text{Detection Voltage}(V_{OUT} \text{ rising}) = \frac{R_1 + R_2}{R_2} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_1 + R_2}{R_2} \times 1.248 \text{ [V]}$$

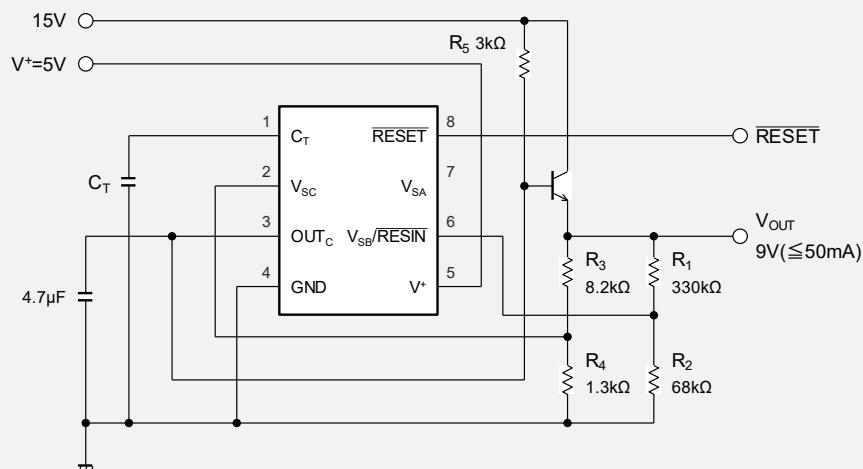


Fig. 11 Reference voltage output and voltage drop monitoring (e.g. 9V reference output, 5V, 9V monitoring)

Technical Information

12-1. Reference Voltage output and Voltage drop monitoring (e.g. 5V output, 5V monitoring)

5V Reference voltage V_{OUT} is generated by V_{SC} (COMP_C), feedback resistors R_3 , R_4 , NPN transistor and drive resistor R_5 , and its 5V is monitored by V_{SA} (COMP_A).

- The reference voltage V_{OUT} is calculated as following formula. In case of resistor value In Fig.12-1, the reference voltage V_{OUT} is about 5.0V

Reference Voltage calculate formula

$$\text{Reference voltage } V_{OUT} = \frac{R_3 + R_4}{R_3} \times V_{SC} \approx \frac{R_3 + R_4}{R_3} \times 1.235 \text{ [V]}$$

- The detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.

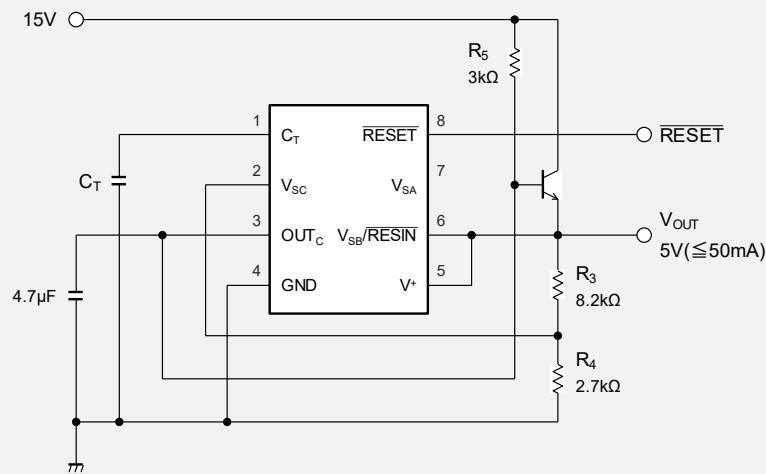


Fig. 12-1 Reference Voltage output and Voltage drop monitoring (e.g. 5V output, 5V monitoring)

Technical Information

12-2. Reference Voltage output and Voltage drop monitoring (e.g. 5V output, 5V monitoring)

5V Reference voltage V_{OUT} is generated by $V_{SC}(\text{COMP_C})$ and feedback resistors R_2 , R_3 , and its 5V is monitored by $V_{SA}(\text{COMP_A})$. Unlike Fig.12-1, 5V output cannot supply large current.

- The reference voltage V_{OUT} is calculated as following formula.

In case of resistor value In Fig.12-2, the reference voltage V_{OUT} is about 5.0V

$$\text{Reference voltage } V_{OUT} = \frac{R_2 + R_3}{R_3} \times V_{SC} \approx \frac{R_2 + R_3}{R_3} \times 1.235 \text{ [V]}$$

- The detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.
- R_1 value should be calculated from current consumption of NJU2103A, the current flowing through R_2 and R_3 , and 5V output current. .

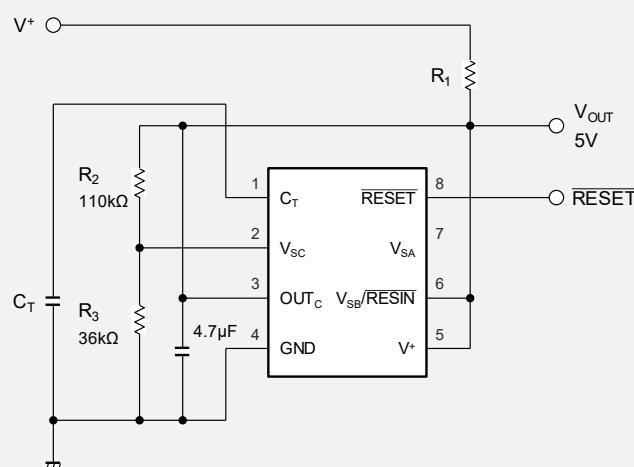


Fig. 12-2 Reference Voltage output and Voltage drop monitoring (e.g. 5V output, 5V monitoring)

13. Reference Voltage output and Voltage drop monitoring (e.g. 1.235V output, 5V monitoring)

Buffer-connect the $V_{SC}(\text{COMP_C})$ and output the reference voltage of COMP_C.

The output current of the reference voltage output is limited by R_1 . If R_1 is 1.2 kΩ, it can output about 2 mA

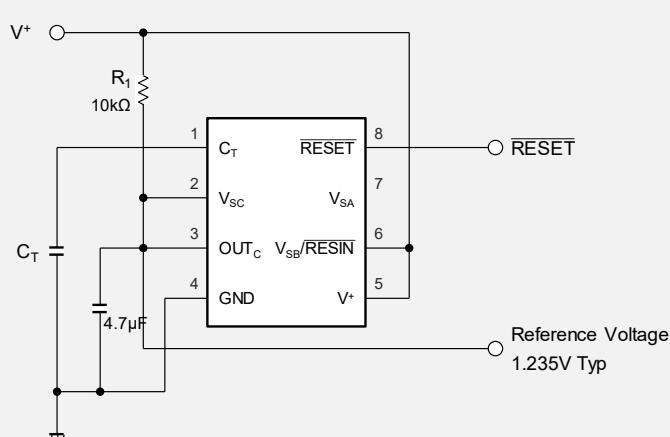


Fig. 13 Reference Voltage output and Voltage drop monitoring (e.g. 1.235V output, 5V monitoring)

Technical Information

14. Low voltage and over voltage detection ($V^+ = 5V$)

V_{SB} (COMP_B) for low voltage detection and V_{SC} (COMP_C) for overvoltage detection.

Logically synthesizes low voltage and over voltage detection by connecting OUT_C to V_{SA} , and output from \overline{RESET} .

- Low voltage detection and over voltage detection are calculated as following formula.

$$\text{Low voltage detection (falling)} \quad V_{SL1} = \frac{R_1 + R_2}{R_2} \times V_{SBL} \approx \frac{R_1 + R_2}{R_2} \times 1.220 \text{ [V]}$$

$$\text{Low voltage detection (rising)} \quad V_{SL2} = \frac{R_1 + R_2}{R_2} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_1 + R_2}{R_2} \times 1.248 \text{ [V]}$$

$$\text{Over voltage detection} \quad V_{SH} = \frac{R_3 + R_4}{R_4} \times V_{SC} \approx \frac{R_3 + R_4}{R_4} \times 1.235 \text{ [V]}$$

- There is no hysteresis characteristics for over voltage detection.
- “ \overline{RESET} Output Pulse Width t_{PO} ” is valid even when overvoltage is detected

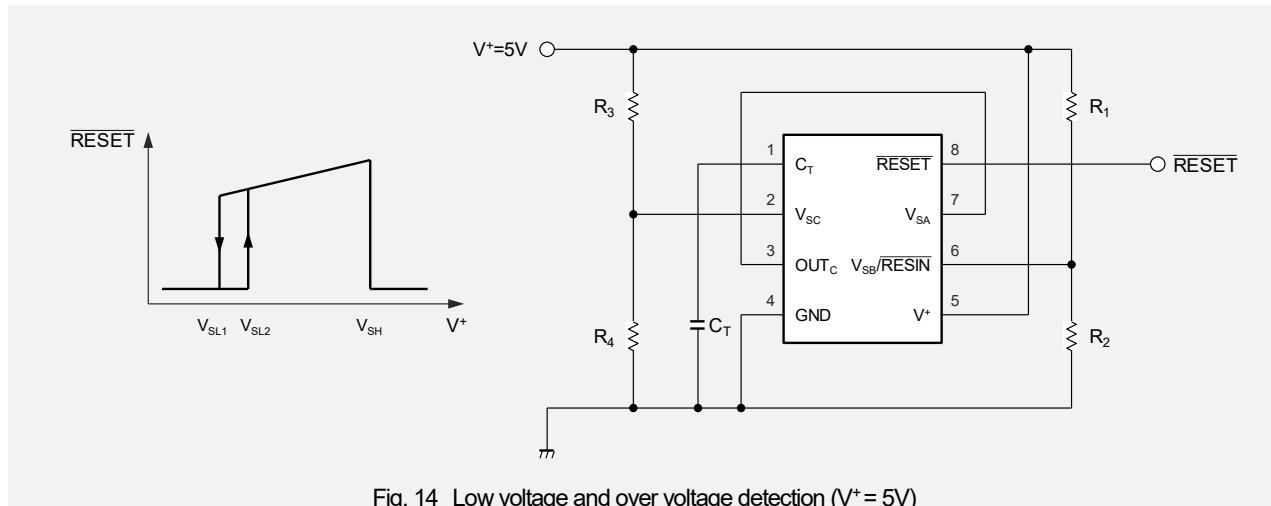
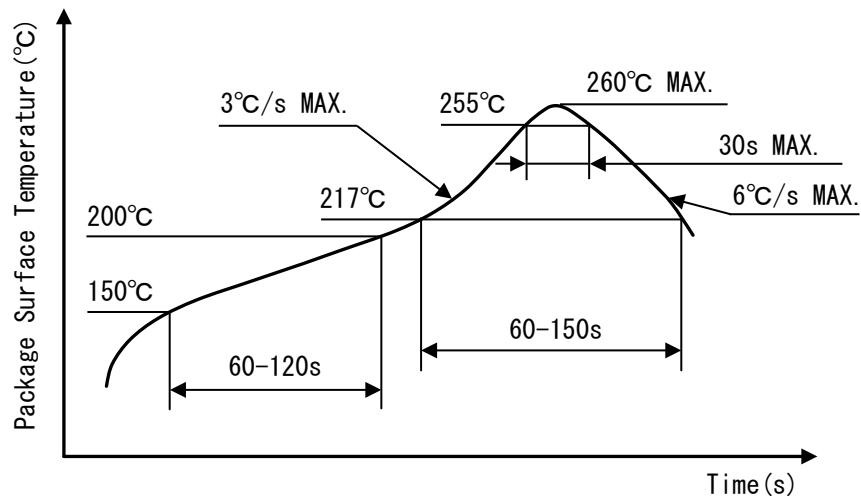


Fig. 14 Low voltage and over voltage detection ($V^+ = 5V$)

Nisshinbo Micro Devices Inc.**■REVISION HISTORY**

Date	Revision	Changes
January.11.2018.	1.0	New Release
August.22. 2018	1.1	Add the Technical Information. (FUNCTION EXPLAMATION, OPERATION EXPLAMATION, APPLICATION EXAMPLE)
Feburary.07. 2019	1.2	Correction of error
January.08.2019	1.3	Change of company name and design form.

■ HEAT-RESISTANCE PROFILES

Reflow profile

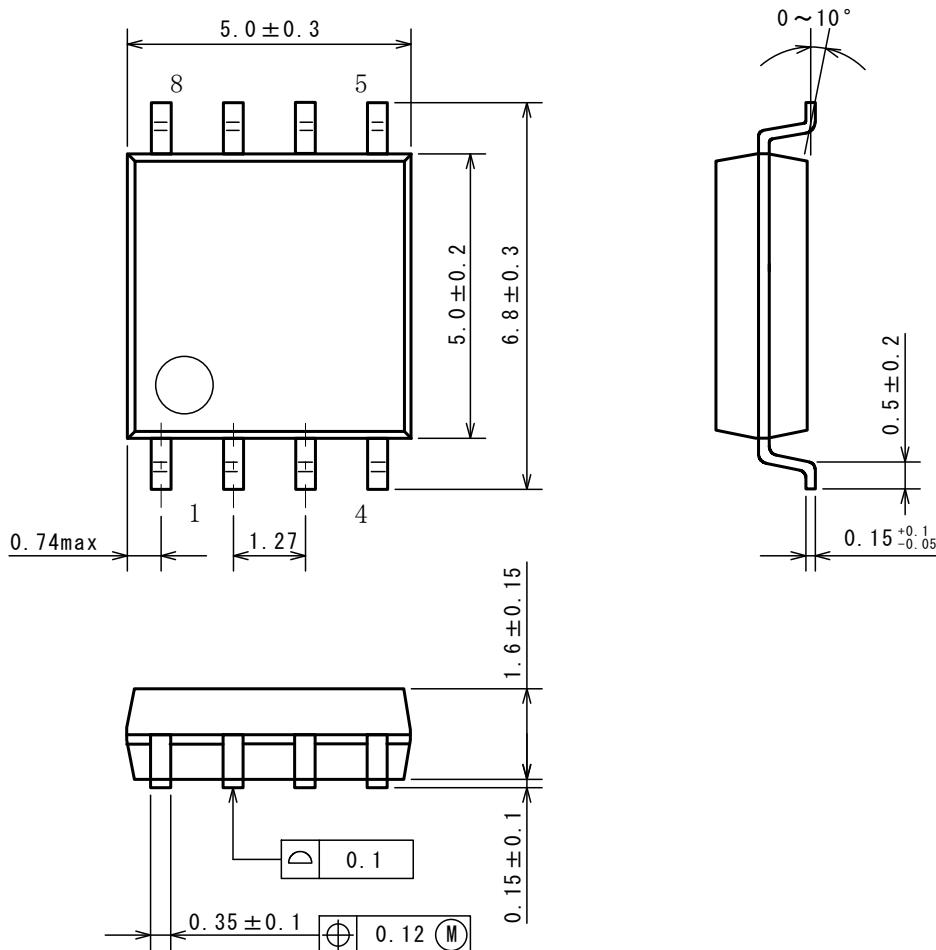
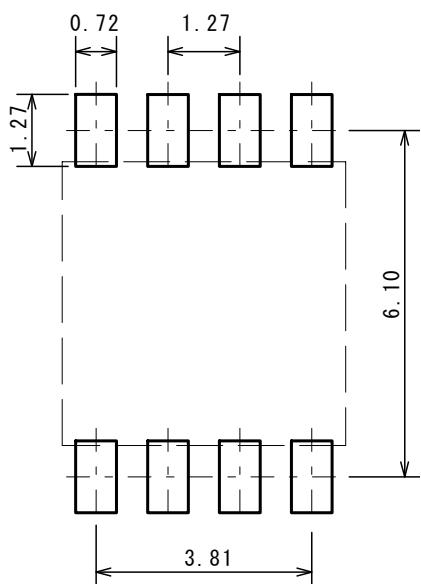
Nissinbo Micro Devices Inc.

DMP8

PI-DMP8-E-B

■ PACKAGE DIMENSIONS

UNIT: mm

**■ EXAMPLE OF SOLDER PADS DIMENSIONS**

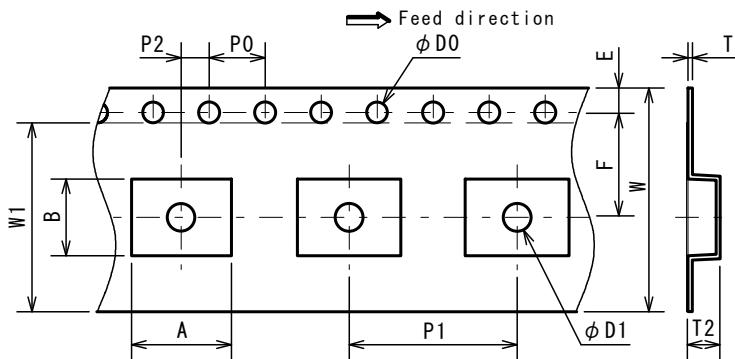
Nissinbo Micro Devices Inc.

DMP8

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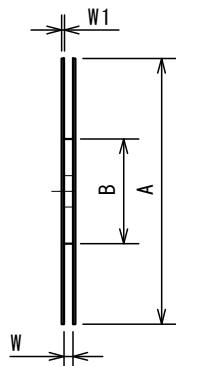
■ PACKING SPEC

TAPING DIMENSIONS



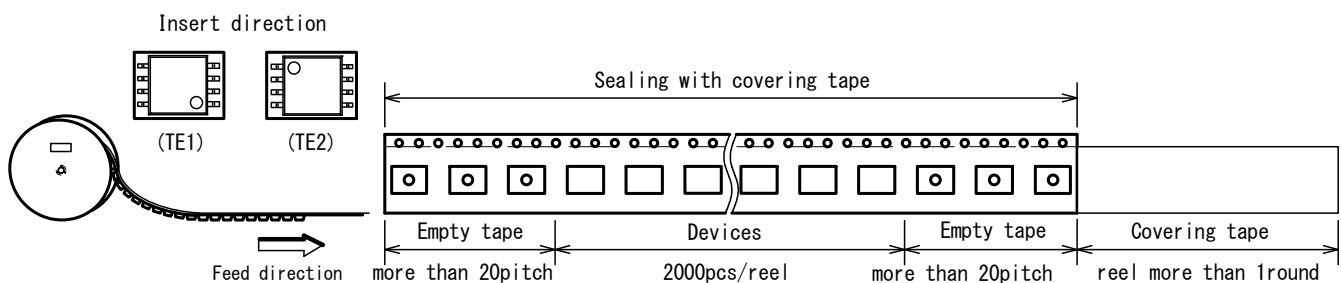
SYMBOL	DIMENSION	REMARKS
A	7.1	BOTTOM DIMENSION
B	5.4	BOTTOM DIMENSION
D0	1.55 ± 0.05	
D1	2.05 ± 0.1	
E	1.75 ± 0.1	
F	7.5 ± 0.1	
P0	4.0 ± 0.1	
P1	12.0 ± 0.1	
P2	2.0 ± 0.1	
T	0.3 ± 0.05	
T2	2.3	
W	16.0 ± 0.3	
W1	13.5	THICKNESS 0.1max

REEL DIMENSIONS

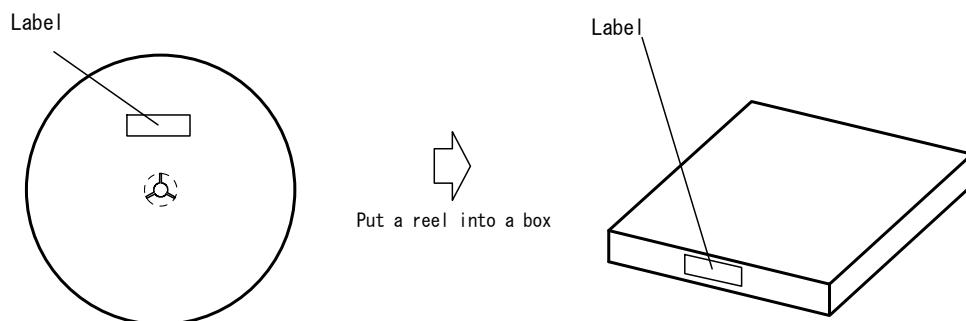


SYMBOL	DIMENSION
A	$\phi 330 \pm 2$
B	$\phi 80 \pm 1$
C	$\phi 13 \pm 0.2$
D	$\phi 21 \pm 0.8$
E	2 ± 0.5
W	17.5 ± 0.5
W1	2 ± 0.2

TAPING STATE



PACKING STATE



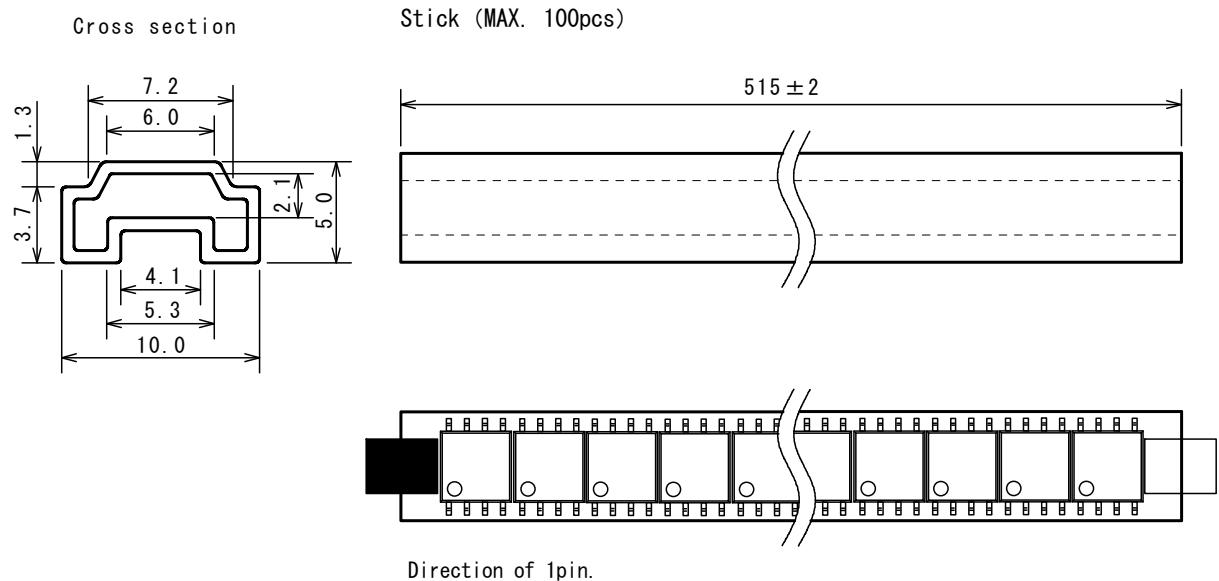
Nissinbo Micro Devices Inc.

DMP8

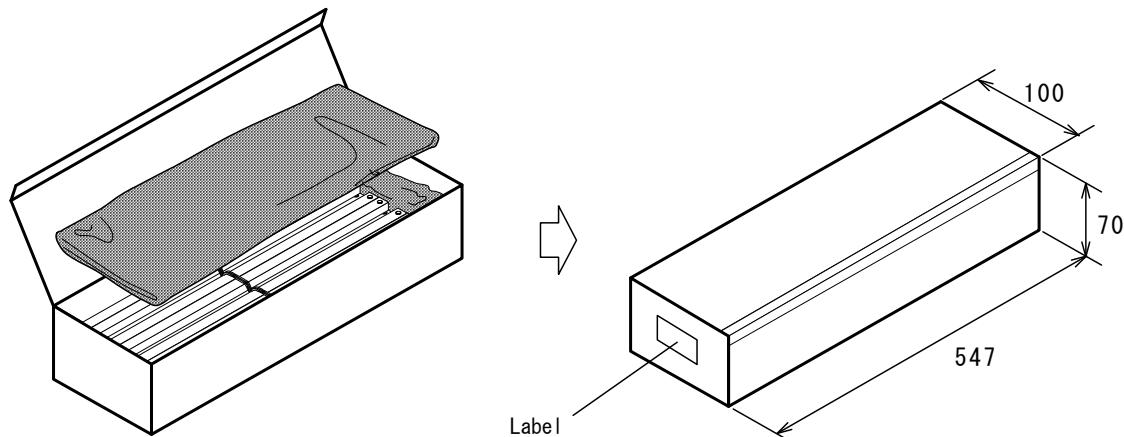
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■ PACKING SPEC

STICK DIMENSIONS



PACKING STATE



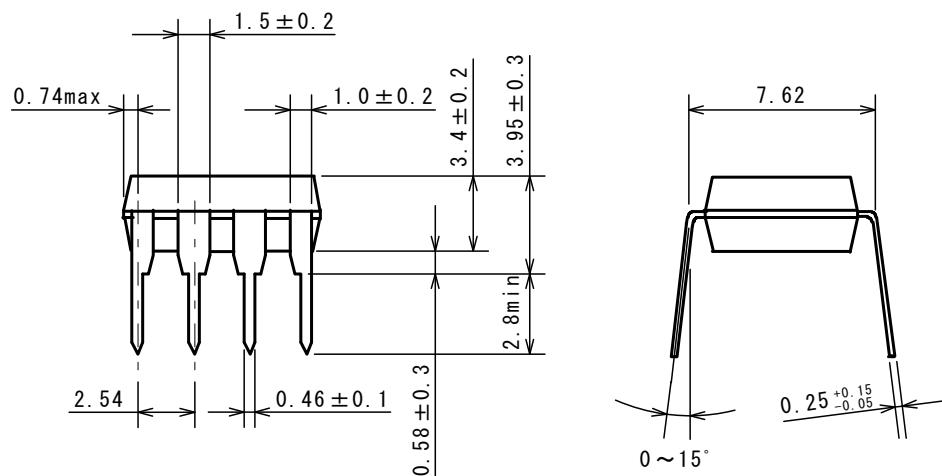
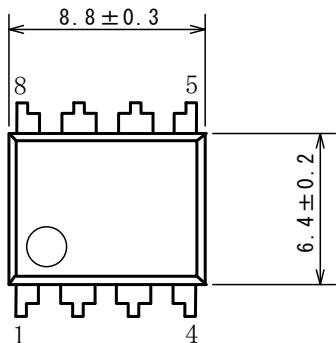
Nissinbo Micro Devices Inc.

DIP8

PI-DIP8-E-A

■ PACKAGE DIMENSIONS

UNIT: mm



Nissinbo Micro Devices Inc.

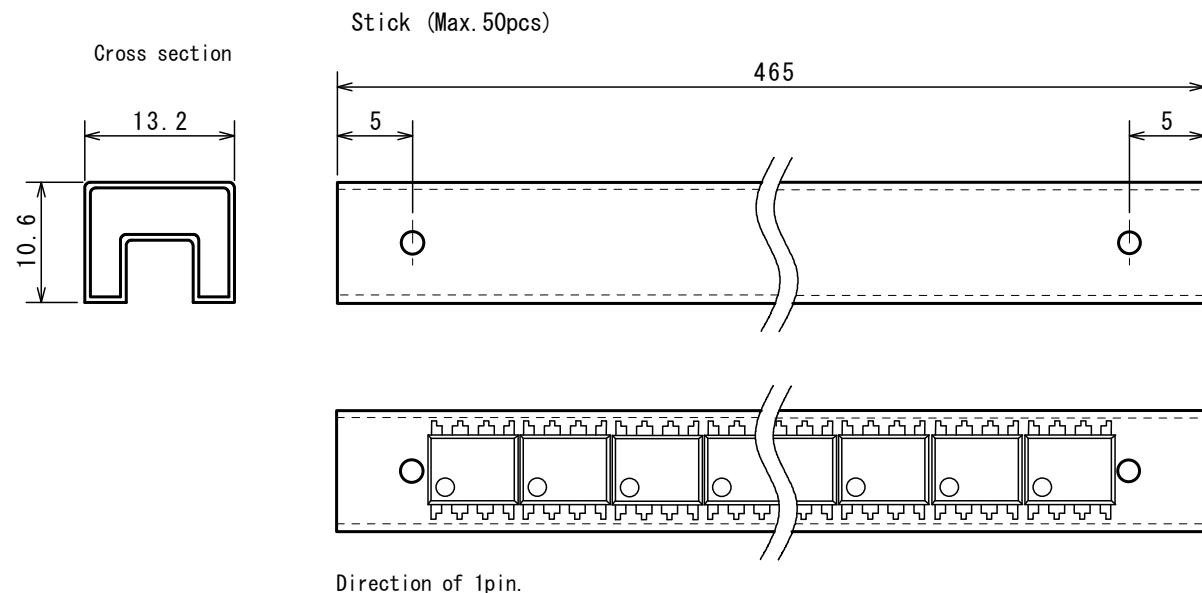
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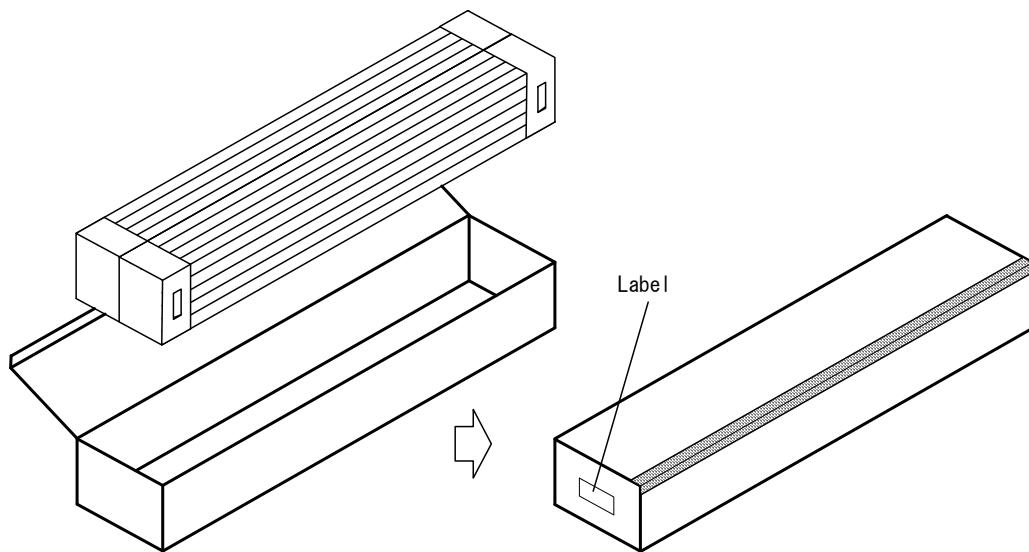
■ PACKING SPEC

STICK STATE

UNIT: mm



PACKING STATE



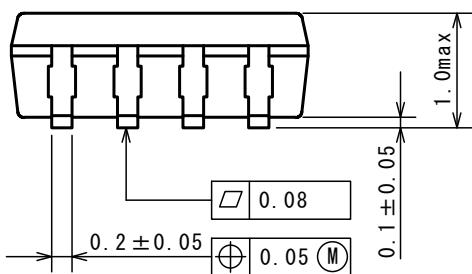
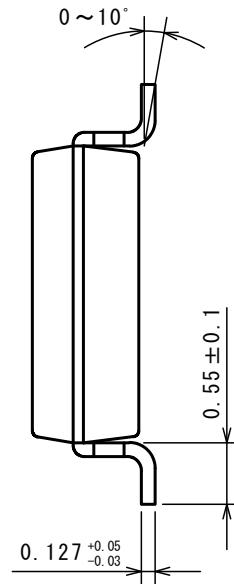
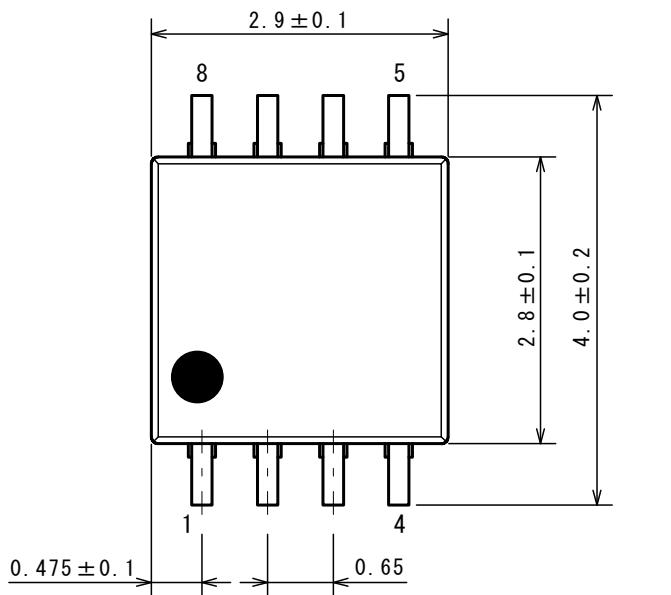
Nissinbo Micro Devices Inc.

MSOP8 MEET JEDEC MO-187-DA / THIN TYPE (TVSP8)

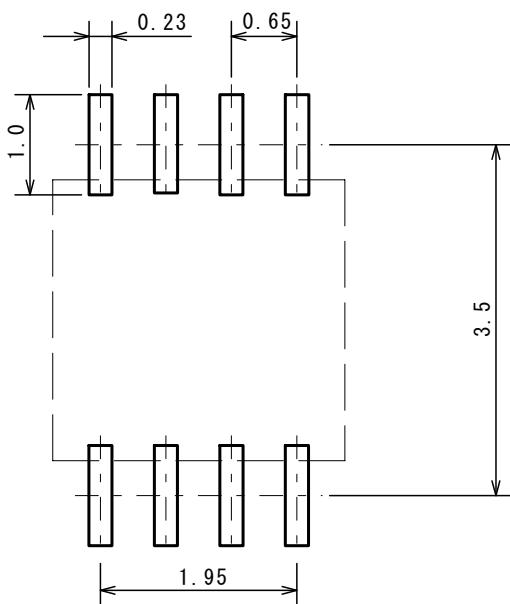
PI-MSOP8 / THIN TYPE-E-A

■ PACKAGE DIMENSIONS

UNIT: mm



■ EXAMPLE OF SOLDER PADS DIMENSIONS



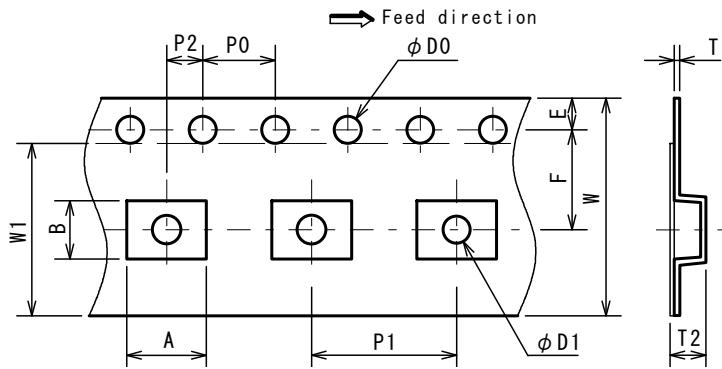
Nissinbo Micro Devices Inc.

MSOP8 MEET JEDEC MO-187-DA / THIN TYPE (TVSP8)

PI-MSOP8 / THIN TYPE-E-A

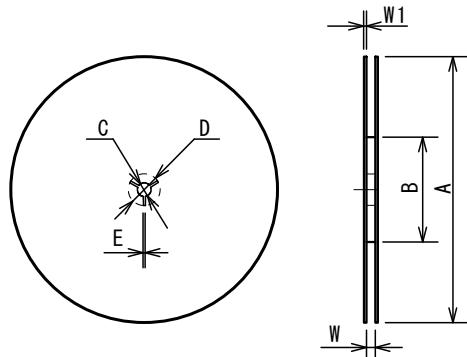
■ PACKING SPEC

TAPING DIMENSIONS



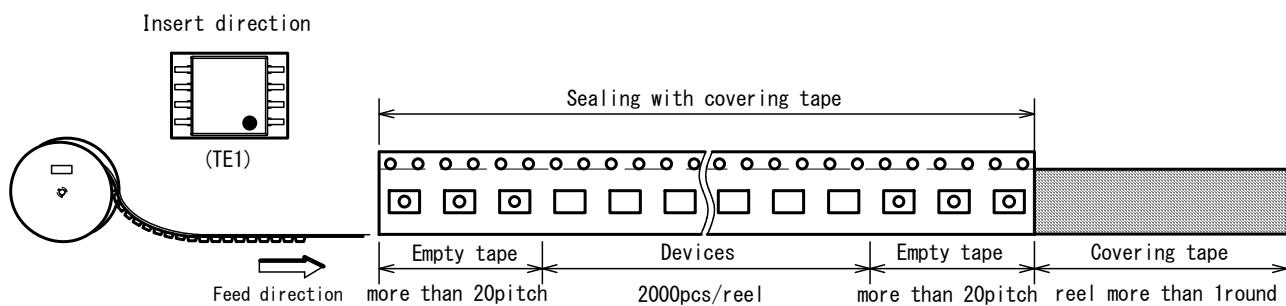
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B	3.2	BOTTOM DIMENSION
D0	$1.5^{+0.1}_0$	
D1	$1.5^{+0.1}_0$	
E	1.75 ± 0.1	
F	5.5 ± 0.05	
P0	4.0 ± 0.1	
P1	8.0 ± 0.1	
P2	2.0 ± 0.05	
T	0.30 ± 0.05	
T2	1.75 (MAX.)	
W	12.0 ± 0.3	
W1	9.5	THICKNESS 0.1max

REEL DIMENSIONS

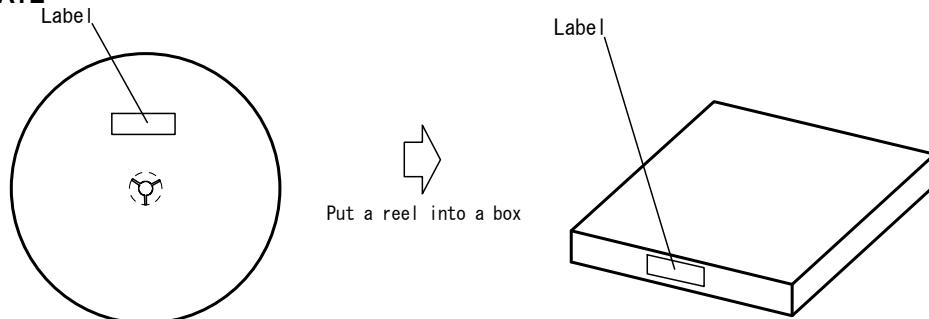


SYMBOL	DIMENSION
A	$\phi 254 \pm 2$
B	$\phi 100 \pm 1$
C	$\phi 13 \pm 0.2$
D	$\phi 21 \pm 0.8$
E	2 ± 0.5
W	13.5 ± 0.5
W1	2.0 ± 0.2

TAPING STATE



PACKING STATE



- The products and the product specifications described in this document are subject to change or discontinuation of production without notice for reasons such as improvement. Therefore, before deciding to use the products, please refer to our sales representatives for the latest information thereon.
- The materials in this document may not be copied or otherwise reproduced in whole or in part without the prior written consent of us.
- This product and any technical information relating thereto are subject to complementary export controls (so-called KNOW controls) under the Foreign Exchange and Foreign Trade Law, and related politics ministerial ordinance of the law. (Note that the complementary export controls are inapplicable to any application-specific products, except rockets and pilotless aircraft, that are insusceptible to design or program changes.) Accordingly, when exporting or carrying abroad this product, follow the Foreign Exchange and Foreign Trade Control Law and its related regulations with respect to the complementary export controls.
- The technical information described in this document shows typical characteristics and example application circuits for the products. The release of such information is not to be construed as a warranty of or a grant of license under our or any third party's intellectual property rights or any other rights.
- The products listed in this document are intended and designed for use as general electronic components in standard applications (office equipment, telecommunication equipment, measuring instruments, consumer electronic products, amusement equipment etc.). Those customers intending to use a product in an application requiring extreme quality and reliability, for example, in a highly specific application where the failure or misoperation of the product could result in human injury or death should first contact us.
 - Aerospace Equipment
 - Equipment Used in the Deep Sea
 - Power Generator Control Equipment (nuclear, steam, hydraulic, etc.)
 - Life Maintenance Medical Equipment
 - Fire Alarms / Intruder Detectors
 - Vehicle Control Equipment (automotive, airplane, railroad, ship, etc.)
 - Various Safety Devices
 - Traffic control system
 - Combustion equipment

In case your company desires to use this product for any applications other than general electronic equipment mentioned above, make sure to contact our company in advance. Note that the important requirements mentioned in this section are not applicable to cases where operation requirements such as application conditions are confirmed by our company in writing after consultation with your company.

- We are making our continuous effort to improve the quality and reliability of our products, but semiconductor products are likely to fail with certain probability. In order to prevent any injury to persons or damages to property resulting from such failure, customers should be careful enough to incorporate safety measures in their design, such as redundancy feature, fire containment feature and fail-safe feature. We do not assume any liability or responsibility for any loss or damage arising from misuse or inappropriate use of the products.
- The products have been designed and tested to function within controlled environmental conditions. Do not use products under conditions that deviate from methods or applications specified in this datasheet. Failure to employ the products in the proper applications can lead to deterioration, destruction or failure of the products. We shall not be responsible for any bodily injury, fires or accident, property damage or any consequential damages resulting from misuse or misapplication of the products.
- Quality Warranty**

8-1. Quality Warranty Period

In the case of a product purchased through an authorized distributor or directly from us, the warranty period for this product shall be one (1) year after delivery to your company. For defective products that occurred during this period, we will take the quality warranty measures described in section 8-2. However, if there is an agreement on the warranty period in the basic transaction agreement, quality assurance agreement, delivery specifications, etc., it shall be followed.

8-2. Quality Warranty Remedies

When it has been proved defective due to manufacturing factors as a result of defect analysis by us, we will either deliver a substitute for the defective product or refund the purchase price of the defective product.

Note that such delivery or refund is sole and exclusive remedies to your company for the defective product.

8-3. Remedies after Quality Warranty Period

With respect to any defect of this product found after the quality warranty period, the defect will be analyzed by us. On the basis of the defect analysis results, the scope and amounts of damage shall be determined by mutual agreement of both parties. Then we will deal with upper limit in Section 8-2. This provision is not intended to limit any legal rights of your company.

- Anti-radiation design is not implemented in the products described in this document.
- The X-ray exposure can influence functions and characteristics of the products. Confirm the product functions and characteristics in the evaluation stage.
- WLCSP products should be used in light shielded environments. The light exposure can influence functions and characteristics of the products under operation or storage.
- Warning for handling Gallium and Arsenic (GaAs) products (Applying to GaAs MMIC, Photo Reflector). These products use Gallium (Ga) and Arsenic (As) which are specified as poisonous chemicals by law. For the prevention of a hazard, do not burn, destroy, or process chemically to make them as gas or power. When the product is disposed of, please follow the related regulation and do not mix this with general industrial waste or household waste.
- Please contact our sales representatives should you have any questions or comments concerning the products or the technical information.



Nisshinbo Micro Devices Inc.

Official website

<https://www.nisshinbo-microdevices.co.jp/en/>

Purchase information

<https://www.nisshinbo-microdevices.co.jp/en/buy/>